

EE 330

Lecture 34

Layout of Current Mirrors

Common-Centroid Layouts

High Gain Amplifiers

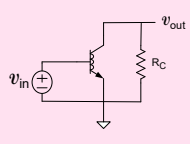
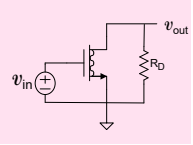
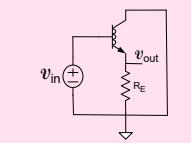
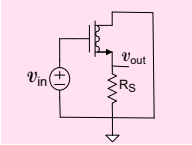
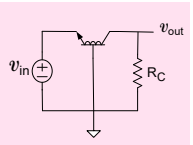
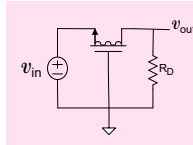
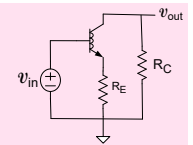
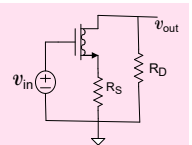
Cascode Amplifiers

Fall 2025 Exam Schedule

Exam 1	Friday	Sept 26
Exam 2	Friday	October 24
Exam 3	Friday	Nov 21
Final Exam	Monday	Dec 15 12:00 - 2:00 PM

Review From Previous Lecture

Basic Amplifier Application Gain Table (for low-frequency operation)

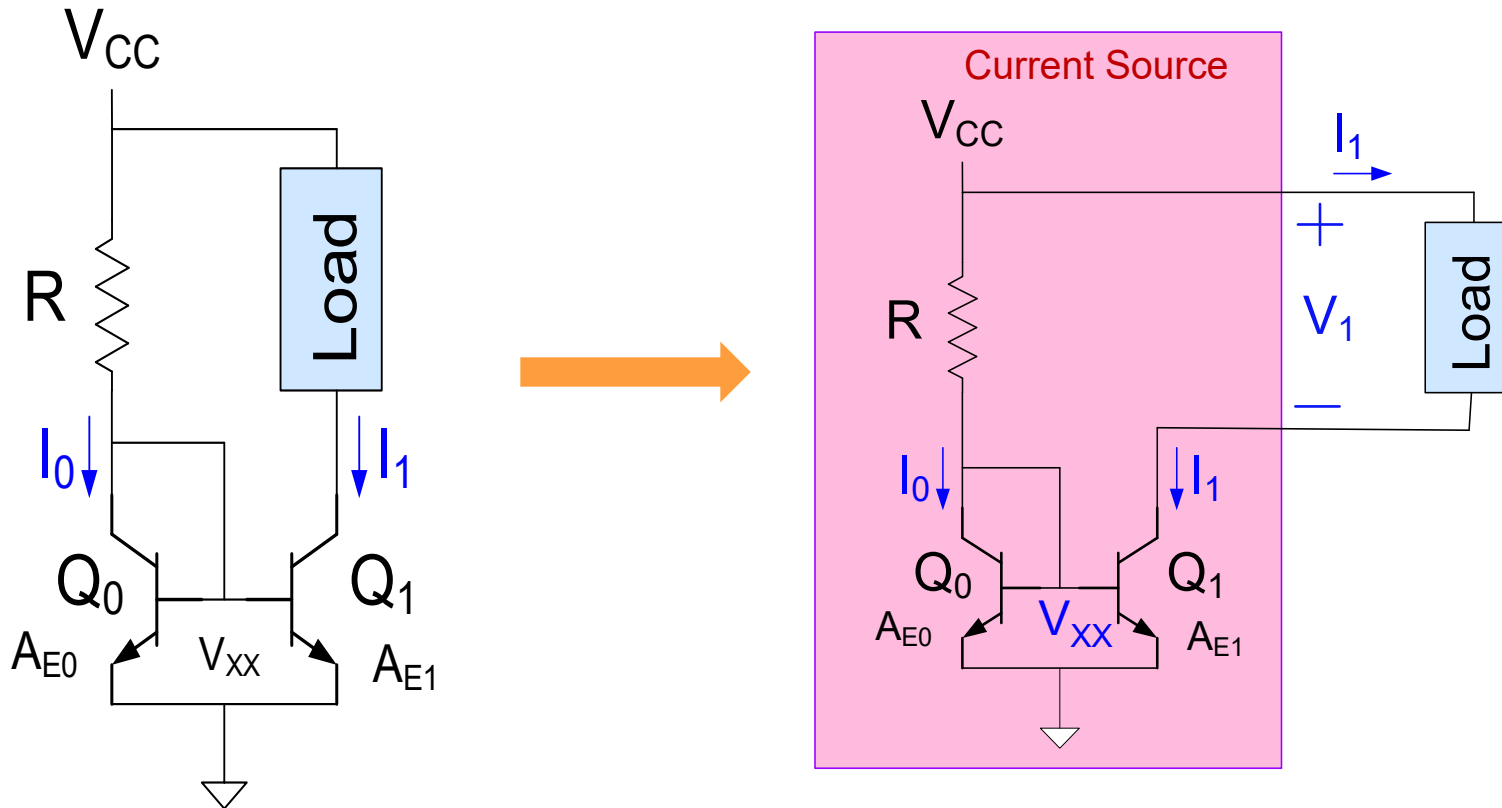
	CE/CS		CC/CD		CB/CG		CEwRE/CSwRS	
	BJT	MOS	BJT	MOS	BJT	MOS	BJT	MOS
A_V	 $-g_m R_C$ $-\frac{I_{CQ} R_C}{V_t}$	 $-\frac{2I_{DQ} R_D}{V_{EB}}$	 $\frac{g_m}{g_m + g_E}$ $\frac{I_{CQ} R_E}{I_{CQ} R_E + V_t}$	 $\frac{2I_{DQ} R_E}{2I_{DQ} R_E + V_{EB}}$	 $g_m R_C$ $\frac{I_{CQ} R_C}{V_t}$	 $\frac{2I_{DQ} R_C}{V_{EB}}$	 $-\frac{R_C}{R_E}$	
R_{in}	r_{π} $\frac{\beta V_t}{I_{CQ}}$	∞	$r_{\pi} + \beta R_E$ $\frac{\beta V_t}{I_{CQ}} + \beta R_E \approx \beta R_E$	∞	g_m^{-1} $\frac{V_t}{I_{CQ}}$	$\frac{V_{EB}}{2I_{DQ}}$	$r_{\pi} + \beta R_E$ $\beta \left(\frac{V_t}{I_{CQ}} + R_E \right) \approx \beta R_E$	∞
R_{out}	R_C		g_m^{-1} $\frac{V_t}{I_{CQ}}$	$\frac{V_{EB}}{2I_{DQ}}$	R_C		R_C	

(not two-port models for the four structures)

Can use these equations only when small signal circuit is **EXACTLY** like that shown !!

Current Sources/Mirrors

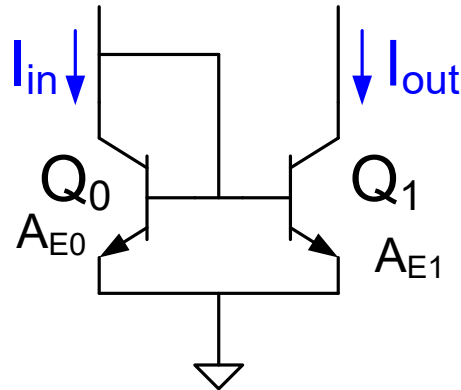
Will show circuit in red behaves as a current source



R and Q_0 simply generate voltage V_{XX} in previous circuit

But sensitivity of I_1 is much smaller than using voltage source for generating V_{XX}

Current Sources/Mirrors



npn Current Mirror

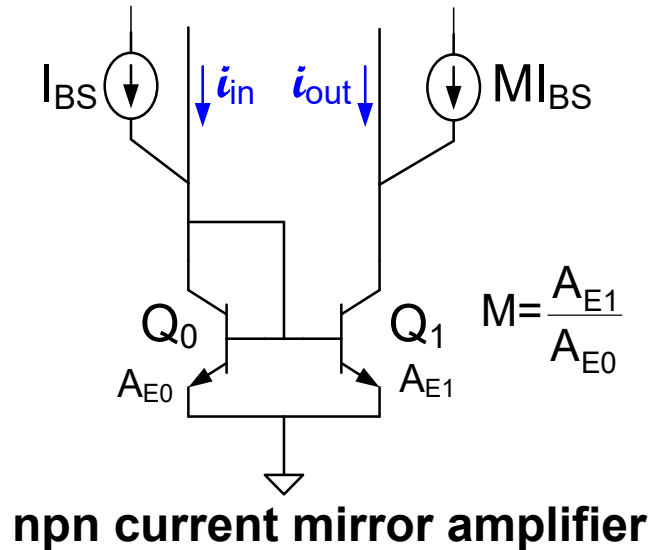
If the base currents are neglected

$$I_{out} = \left[\frac{A_{E1}}{A_{E0}} \right] I_{in}$$

- Output current linearly dependent on I_{in}
- Small-signal and large-signal relationships the same since linear
- Serves as a current amplifier
- Widely used circuit

But I_{in} must be positive !

Current Sources/Mirrors



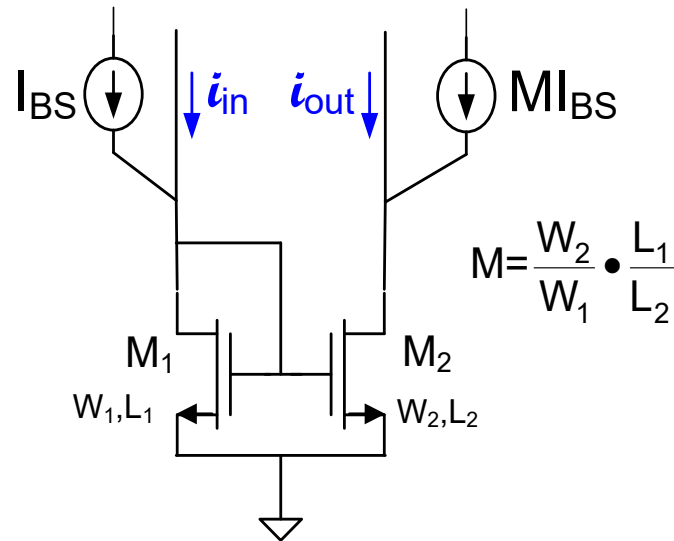
$$i_{\text{out}} = \left[\frac{A_{E1}}{A_{E0}} \right] i_{\text{in}}$$

Amplifies both positive and negative currents (provided $i_{\text{IN}} > -I_{\text{BS}}$)

Current amplifiers are easy to build !!

Current gain can be accurately controlled with appropriate layout !!

n-channel current mirror current amplifier

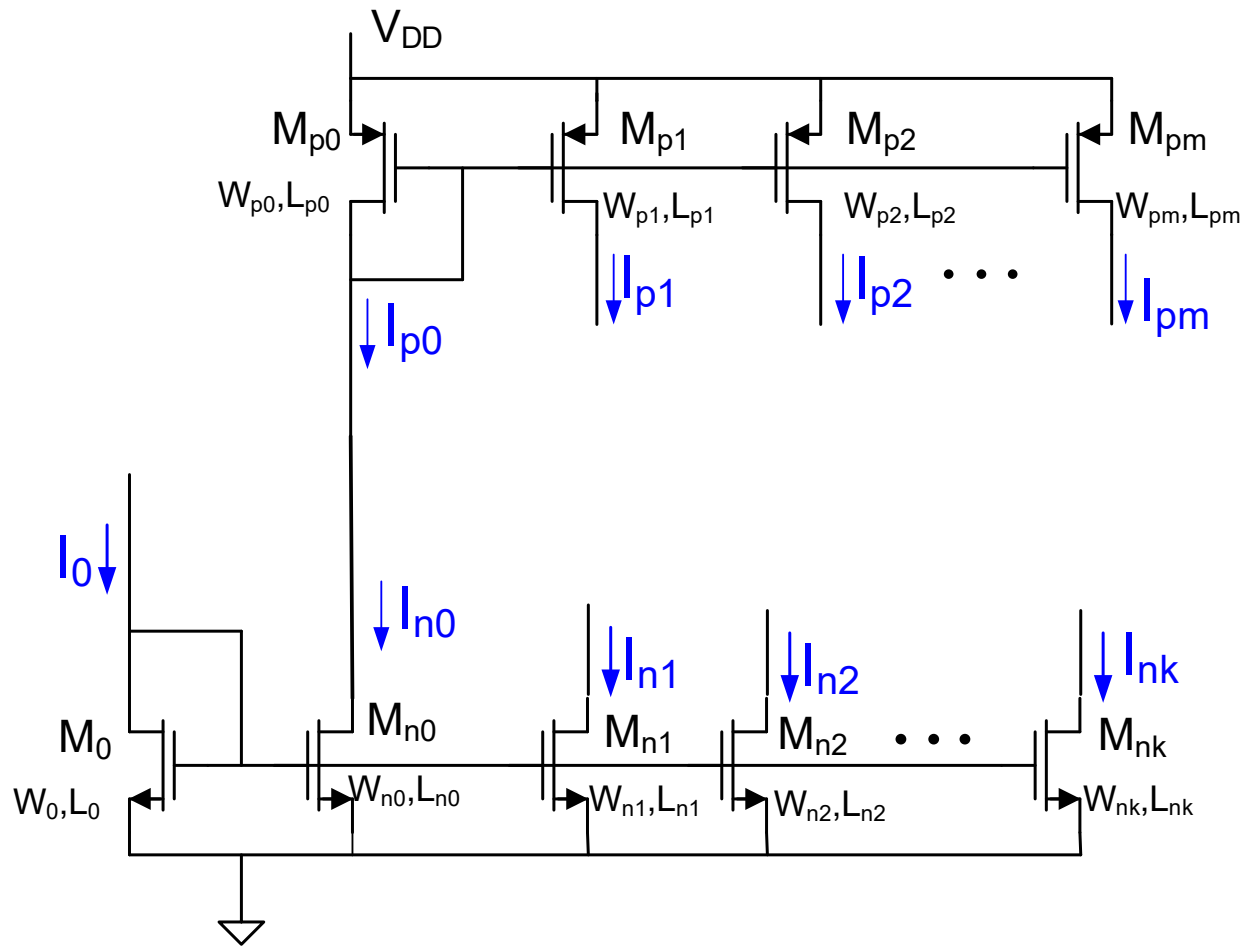


$$i_{out} = \left[\frac{W_2}{W_1} \frac{L_1}{L_2} \right] i_{in}$$

Amplifies both positive and negative currents

Current Sources/Mirrors

multiple sourcing and sinking current outputs



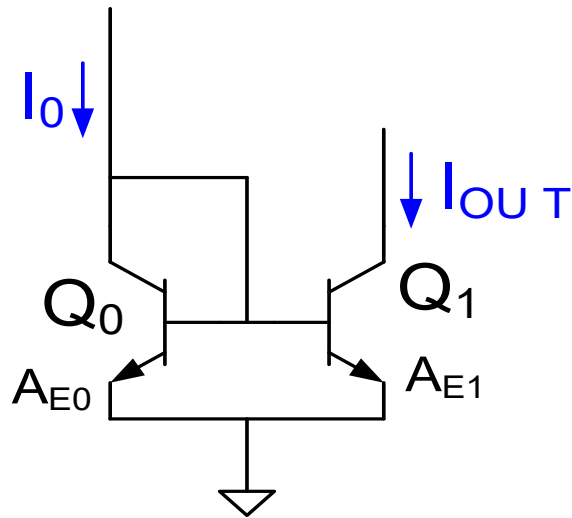
$$I_{pj} = \left[\frac{W_{pj}}{L_{pj}} \cdot \frac{L_{p0}}{W_{p0}} \right] M I_0$$

$$M = \left[\frac{W_{n0}}{L_{n0j}} \cdot \frac{L_0}{W_0} \right]$$

$$I_{nj} = \left[\frac{W_{nj}}{L_{nj}} \cdot \frac{L_0}{W_0} \right] I_0$$

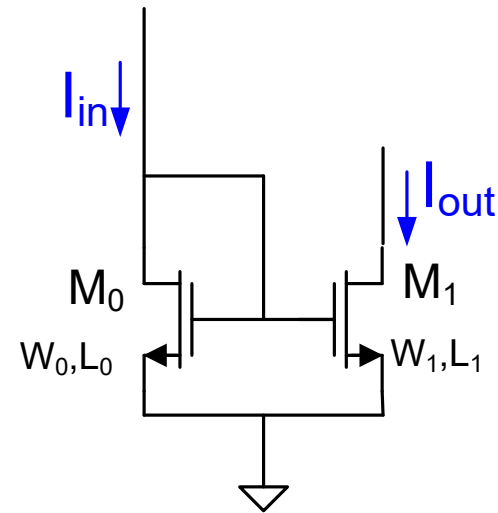
m and k may be different
Often $M=1$

Current Sources/Mirrors Summary



npn Current Mirror

$$I_{out} = \left[\frac{A_{E1}}{A_{E0}} \right] I_{in}$$



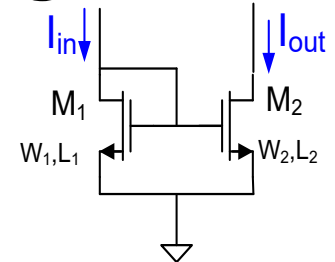
n-channel Current Mirror

$$I_{out} = \left[\frac{W_1}{W_0} \frac{L_0}{L_1} \right] I_{in}$$

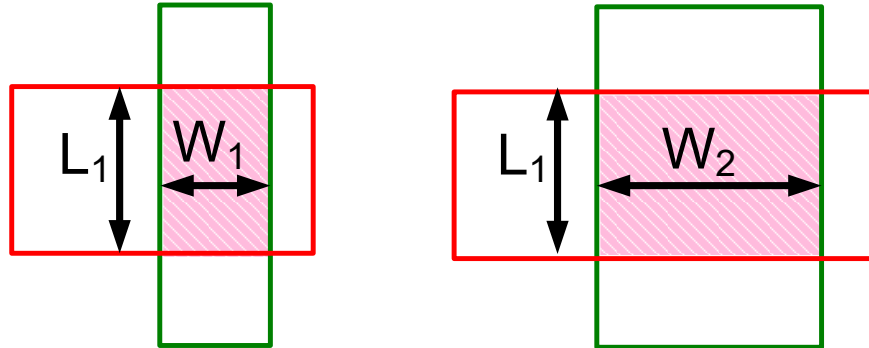
- Current mirror gain can be accurately controlled !
- Layout is important to get accurate gain (for both MOS and BJT)

Layout of Current Mirrors

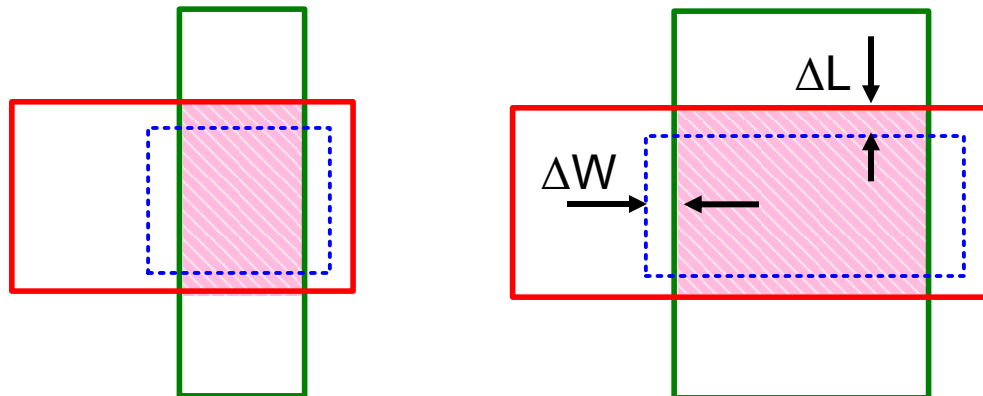
Example with $M = 2$



$$M = \left[\frac{W_2}{W_1} \frac{L_1}{L_2} \right]$$



Standard layout



Gate area after fabrication depicted 

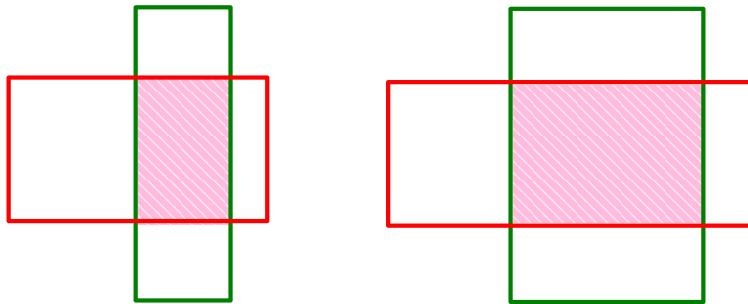
ΔL and ΔW can be positive or negative

$$M = \left[\frac{W_2 + 2\Delta W}{W_1 + 2\Delta W} \cdot \frac{L_1 + 2\Delta L}{L_2 + 2\Delta L} \right]$$

$$M = \left[\frac{2W_1 + 2\Delta W}{W_1 + 2\Delta W} \cdot \frac{L_1 + 2\Delta L}{L_1 + 2\Delta L} \right] \neq 2$$

Layout of Current Mirrors

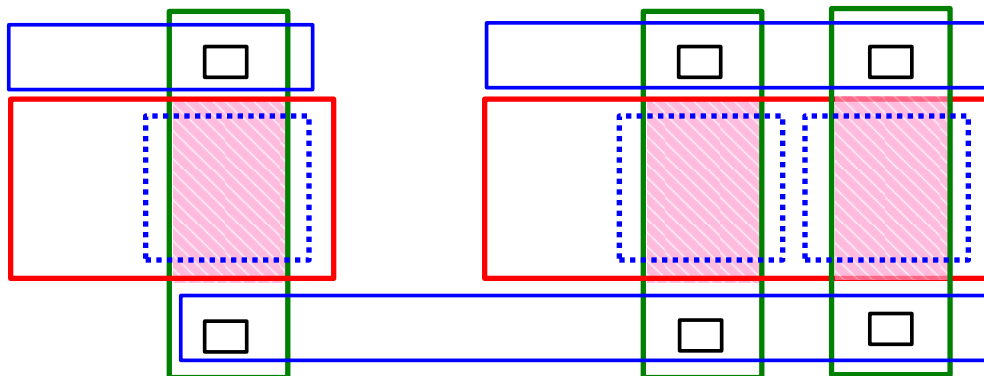
Example with $M = 2$



Standard layout

$$M = \left[\frac{W_2}{W_1} \frac{L_1}{L_2} \right]$$

$$M = \left[\frac{2W_1 + 2\Delta W}{W_1 + 2\Delta W} \cdot \frac{L_1 + 2\Delta L}{L_1 + 2\Delta L} \right] \neq 2$$

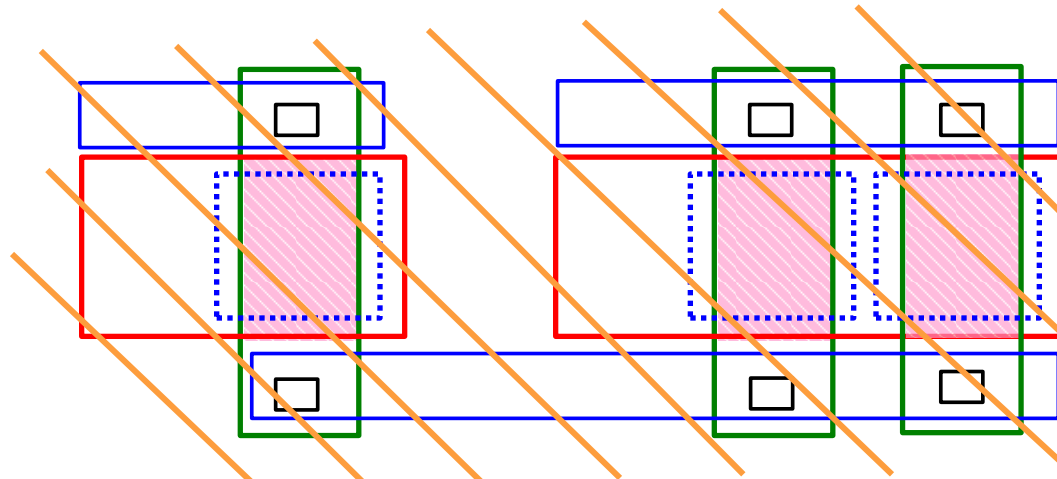


Better Layout

$$M = \left[\frac{2W_1 + 4\Delta W}{W_1 + 2\Delta W} \cdot \frac{L_1 + 2\Delta L}{L_1 + 2\Delta L} \right] = 2$$

Layout of Current Mirrors

Example with $M = 2$



Better Layout

Linear Gradient Direction
of a model parameter
(e.g. μ or V_{TH})

$$M = \left[\frac{2W_1 + 4\Delta W}{W_1 + 2\Delta W} \cdot \frac{L_1 + 2\Delta L}{L_1 + 2\Delta L} \right] = 2$$

But this analysis was based upon assumption of matching of process parameters

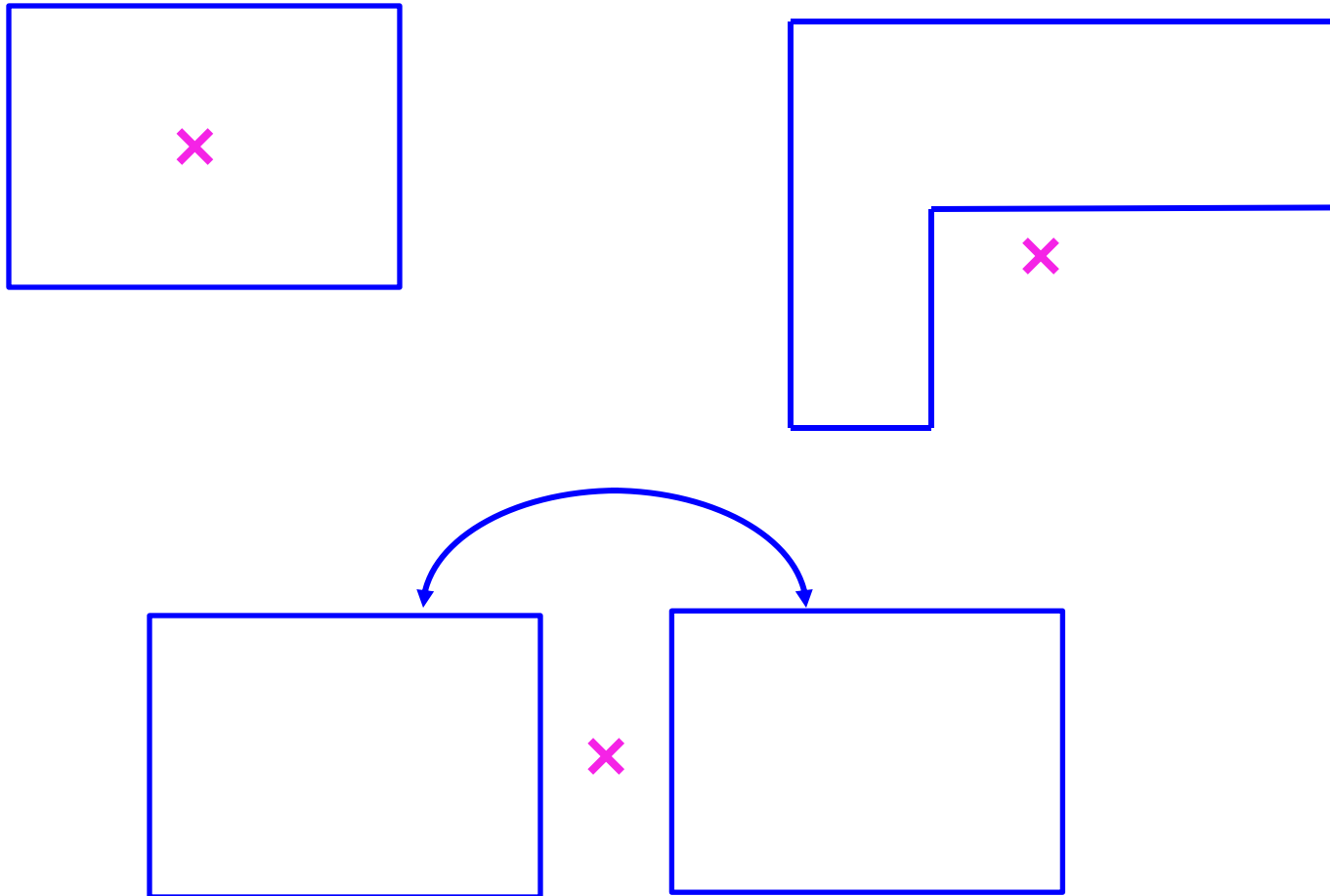
$$\left. \begin{aligned} I_{in} &= \frac{\mu_0 C_{OX} W_0}{2L_0} (V_{GS0} - V_{T0})^2 \\ I_{out} &= \frac{\mu_1 C_{OX} W_1}{2L_1} (V_{GS1} - V_{T1})^2 \end{aligned} \right\}$$

Even with this better layout, the current ratio will not be 2 if gradient effects such as those depicted here are shown

And both magnitude and direction of gradient effects are a random variable which will vary across a die

Centroid and Common Centroid

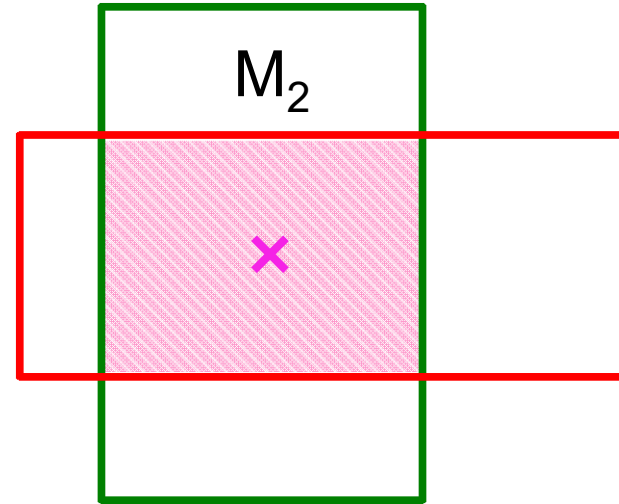
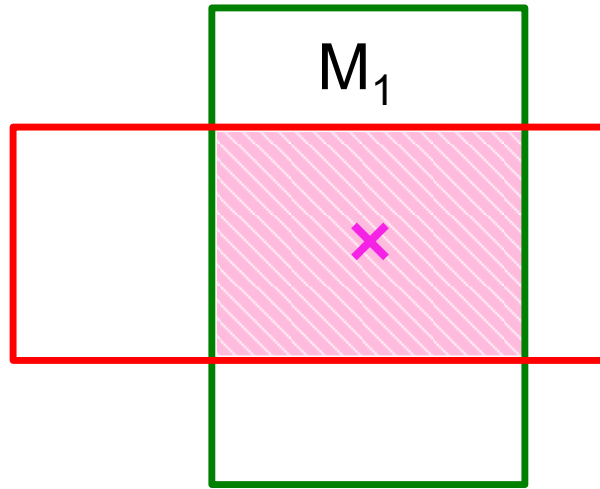
✕ Denotes Geometric Centroid



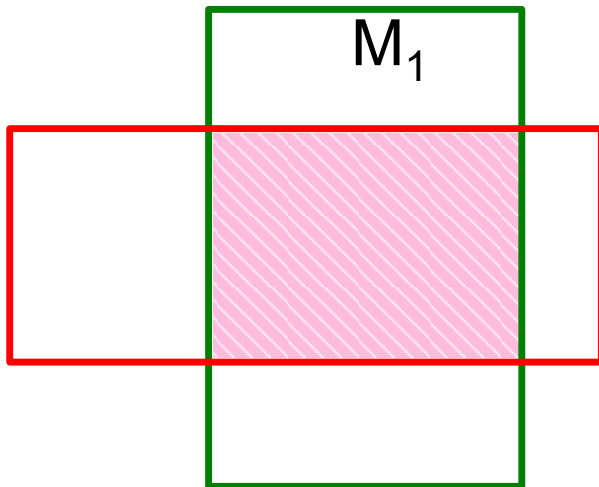
Centroid and Common Centroid

Geometric Centroids of Channel

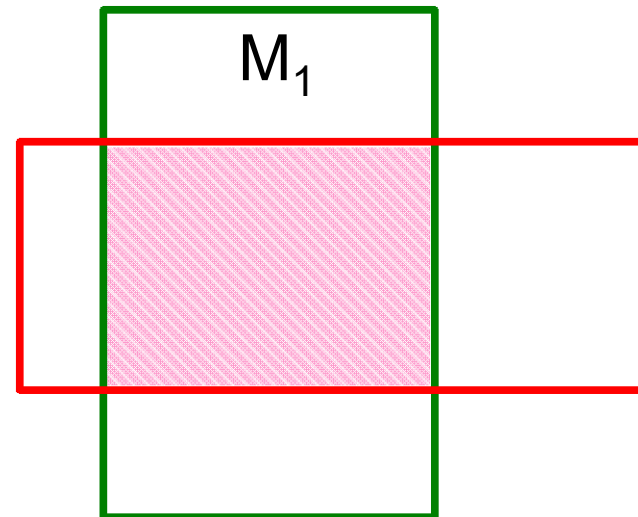
Two Transistors:



Two Parts of One Transistor:

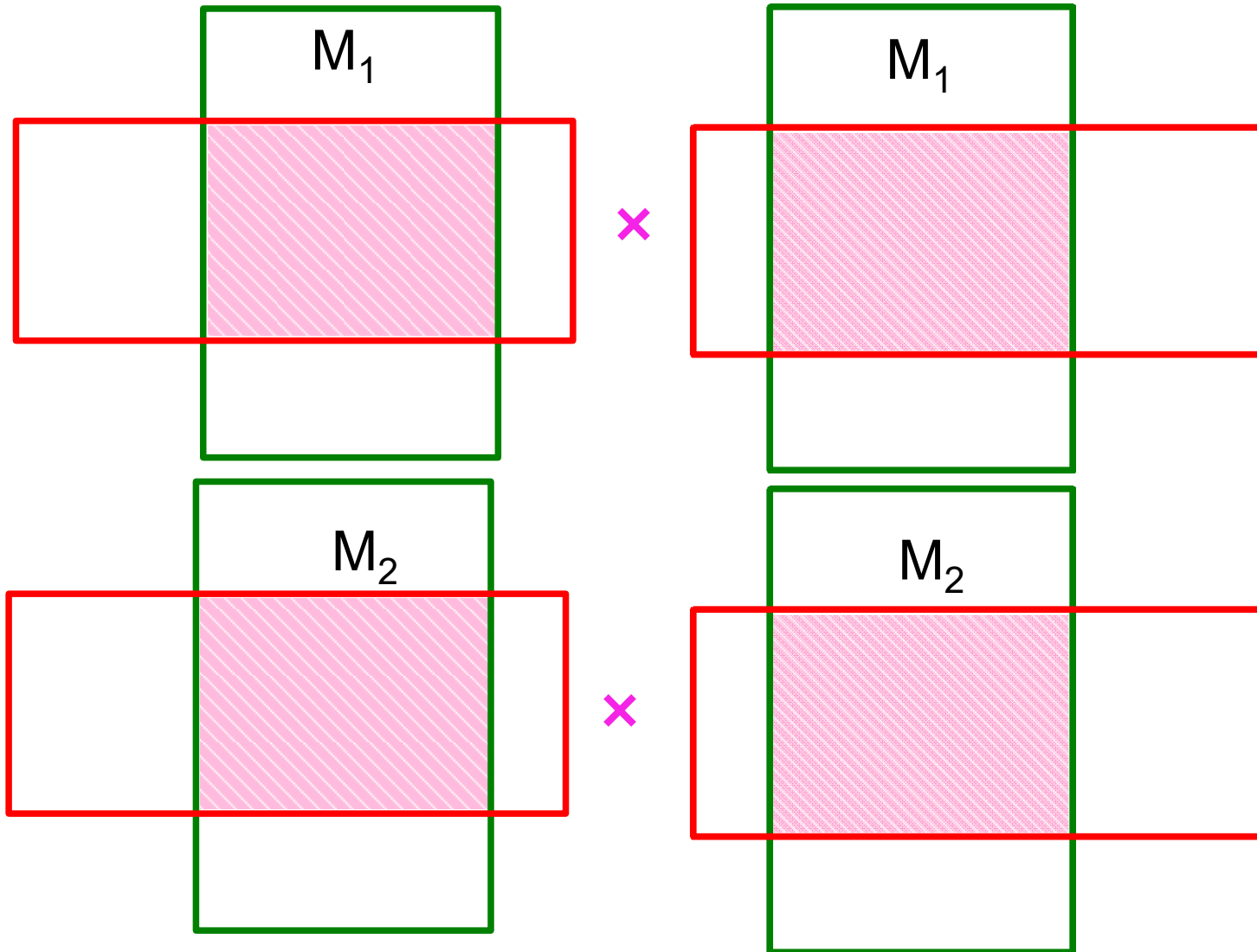


x



Centroid and Common Centroid

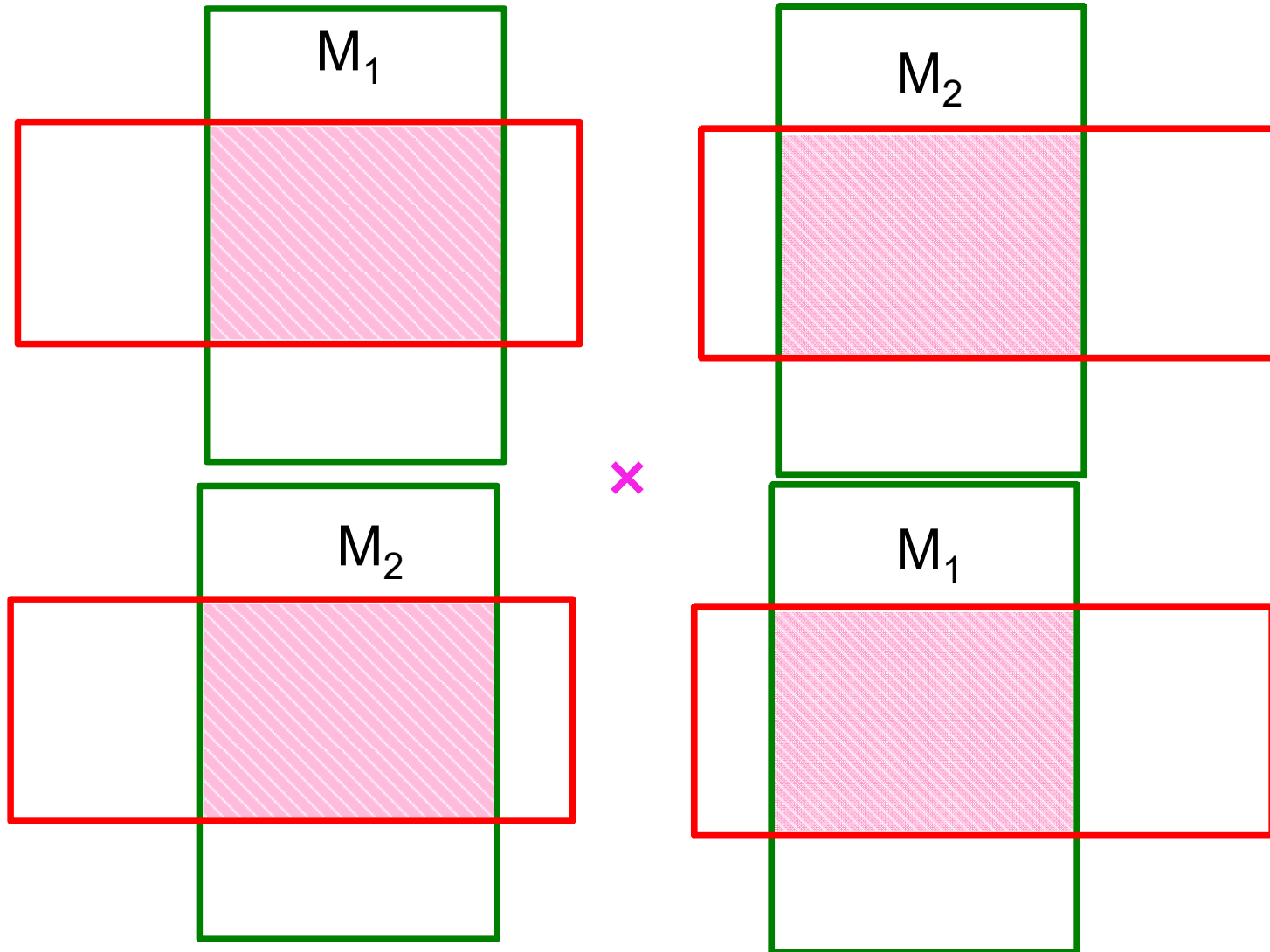
Two Transistors each with two parts:



Centroid and Common Centroid

Common Centroid for Ideally Matched Devices

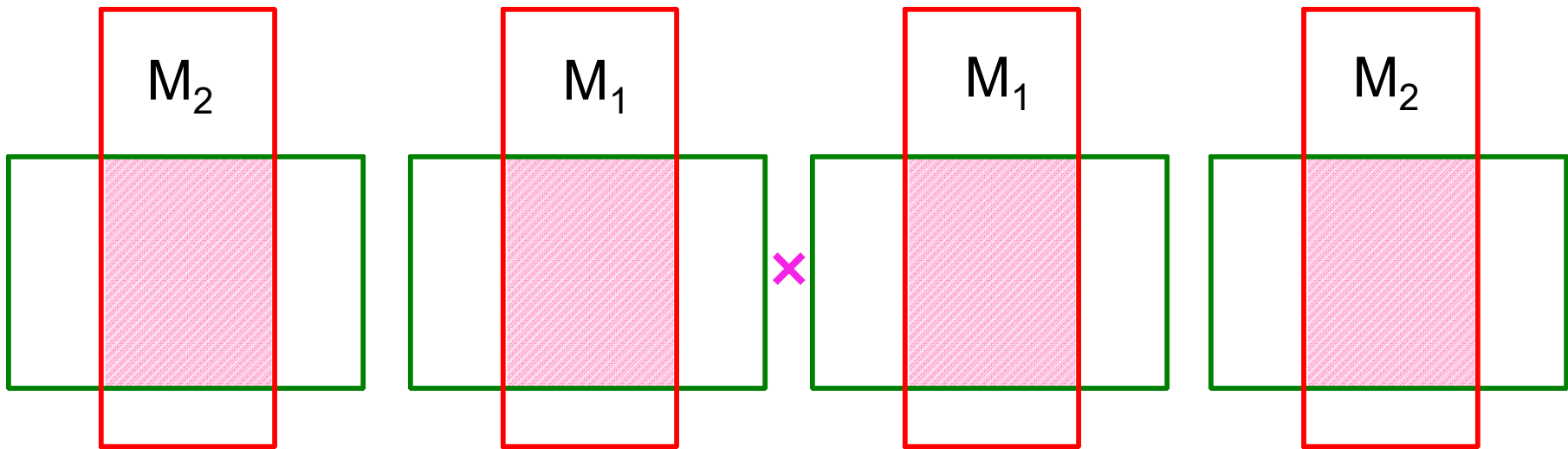
Two Transistors each with two parts:



Centroid and Common Centroid

Common Centroid for Matched Devices

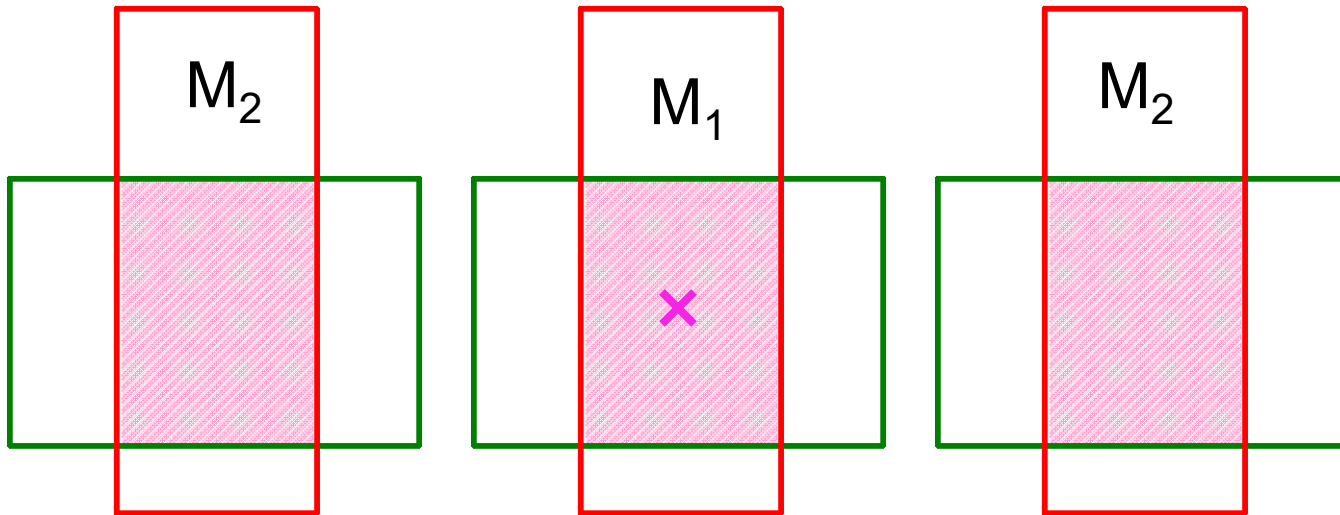
Two Transistors each with two parts:



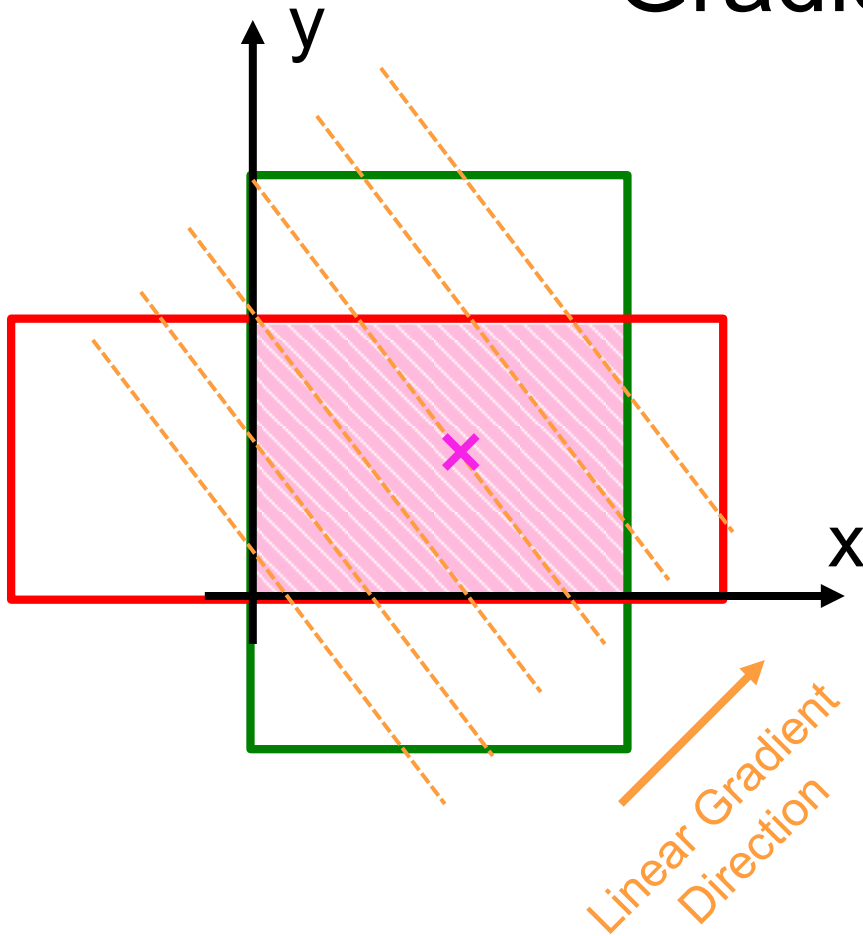
Centroid and Common Centroid

Common Centroid for Ratioed Devices $M = \frac{W_2}{W_1} \frac{L_1}{L_2} = 2$

Two Transistors with different effective widths:



Gradient



Threshold voltage
dependent upon position

$$V_{TH}(x,y)$$

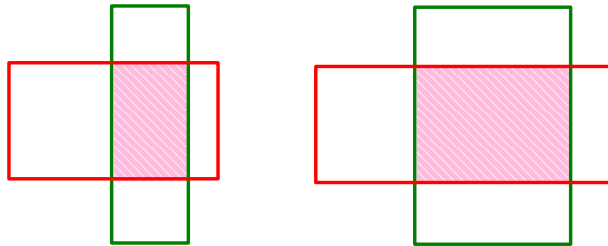
- Significant changes in threshold voltage can occur due to gradient effects
- This can seriously degrade matching in matching-critical circuits
- Gradients in key parameters (V_{TH} , μC_{OX}) usually nearly linear

- If the threshold voltage of a transistor changes with position, it can be reasonably accurately modeled with an “equivalent” threshold voltage
- For linear gradient, $V_{THEQ} = V_{TH}(X_C, Y_C)$

✕ : (X_C, Y_C)

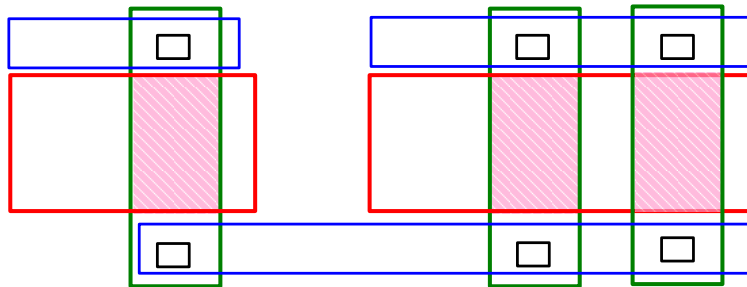
Layout of Current Mirrors

Example with $M = 2$



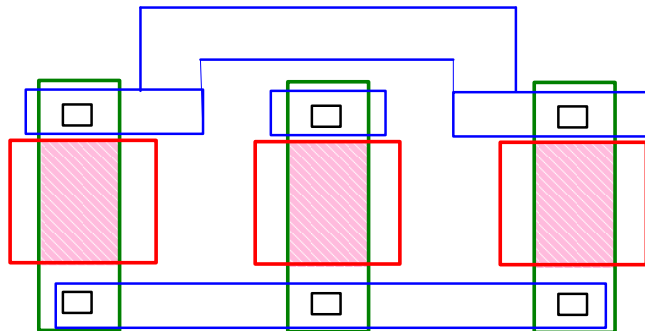
Standard layout

$$M = \left[\frac{W_2}{W_1} \frac{L_1}{L_2} \right]$$



Better Layout

$$M = \left[\frac{2W_1 + 4\Delta W}{W_1 + 2\Delta W} \cdot \frac{L_1 + 2\Delta L}{L_1 + 2\Delta L} \right] = 2$$



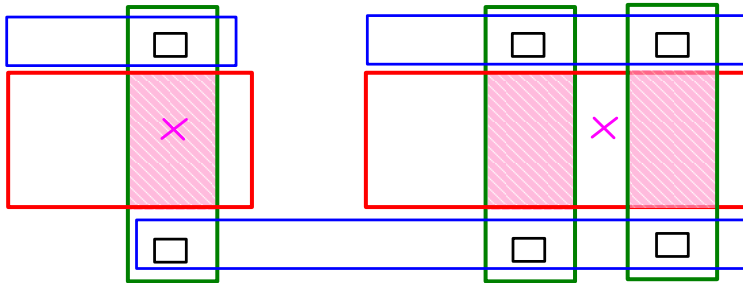
Even Better Layout

$$M = \left[\frac{2W_1 + 4\Delta W}{W_1 + 2\Delta W} \cdot \frac{L_1 + 2\Delta L}{L_1 + 2\Delta L} \right] = 2$$

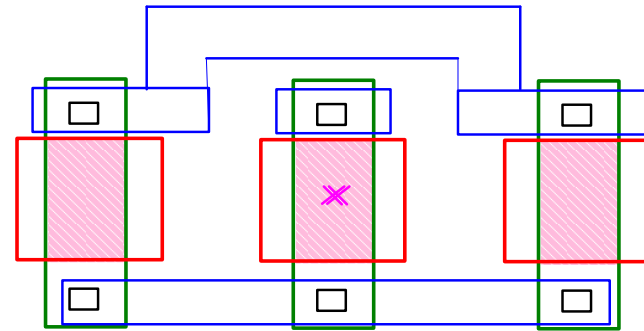
- This is termed a **common-centroid layout**

Layout of Matching-Critical Circuits

Example with $M = 2$



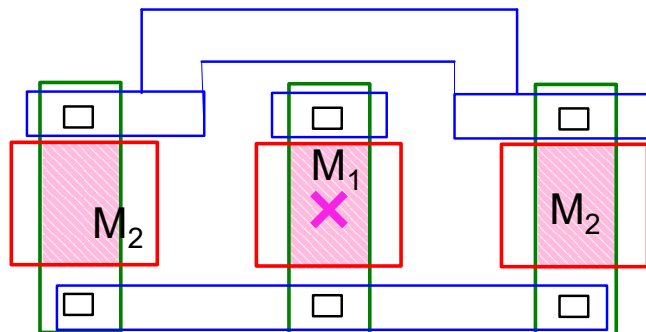
Better Layout



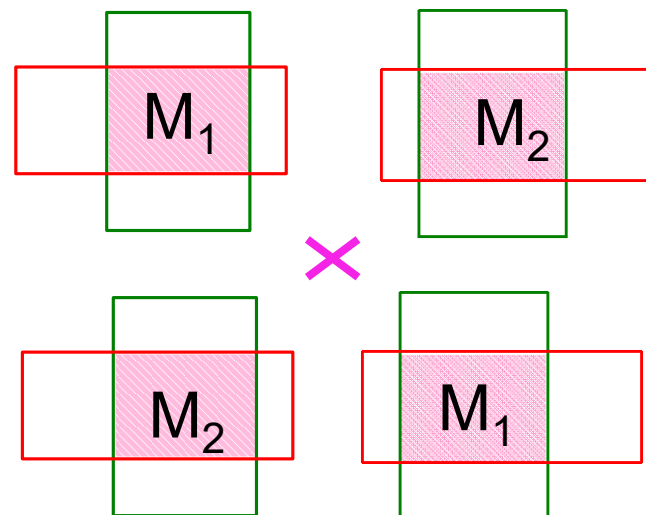
Common-centroid Layout

Theorem: Linear gradient mismatch eliminated with common-centroid layout !

Common-Centroid Layouts



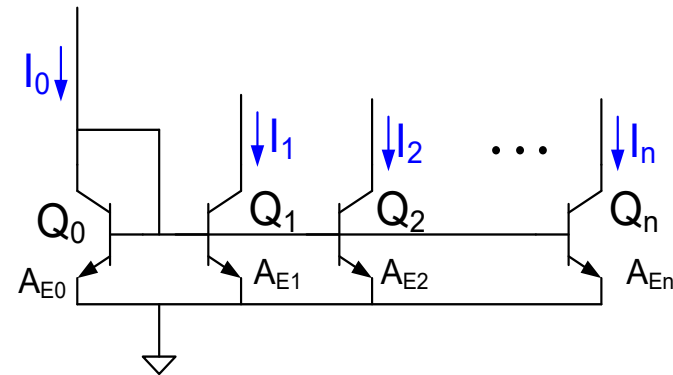
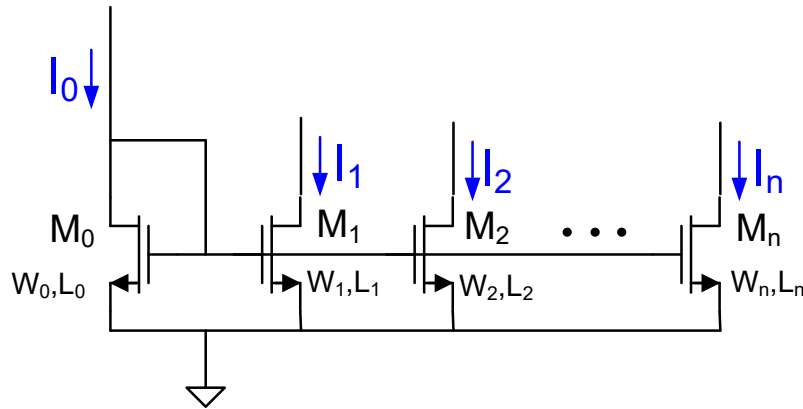
$$M = \left[\frac{2W_1}{W_1} \bullet \frac{L_1}{L_1} \right] = 2$$



$$M = \left[\frac{2W_1}{2W_1} \bullet \frac{L_1}{L_1} \right] = 1$$

- Individual transistors in matching-critical circuits often decomposed into multiple parallel unary devices connected in parallel and placed with common centroid
- Common-Centroid layout approach widely used to minimize (ideally cancel) linear gradient effects in matching-critical circuits
- Applications extend well beyond current mirrors
- More than 2 devices can share a common centroid

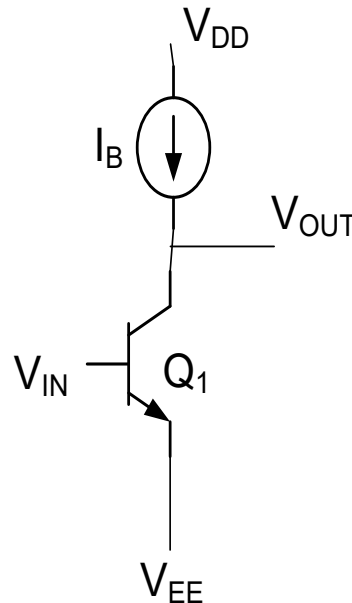
Current Sources/Mirrors



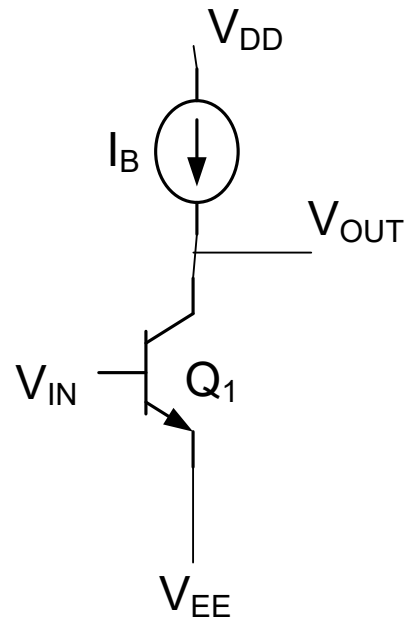
If I_0 is practically generated (it can be), now have available a large number of accurate current sources or sinks that can be used for biasing and for other purposes on chip !

High-gain amplifier

Will now return to discussion of high gain amplifiers



High-gain amplifier



$$A_V \cong -8000$$

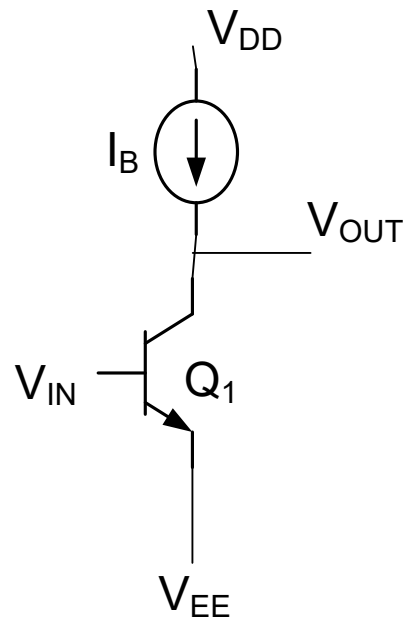
Why are we interested in high-gain amplifiers?

- High gain amplifiers typically have some very undesirable properties

Nonlinear, gain highly dependent upon process variations and temperature, frequency response poor, noisy,

- So we can build feedback amplifiers !!

High-gain amplifier



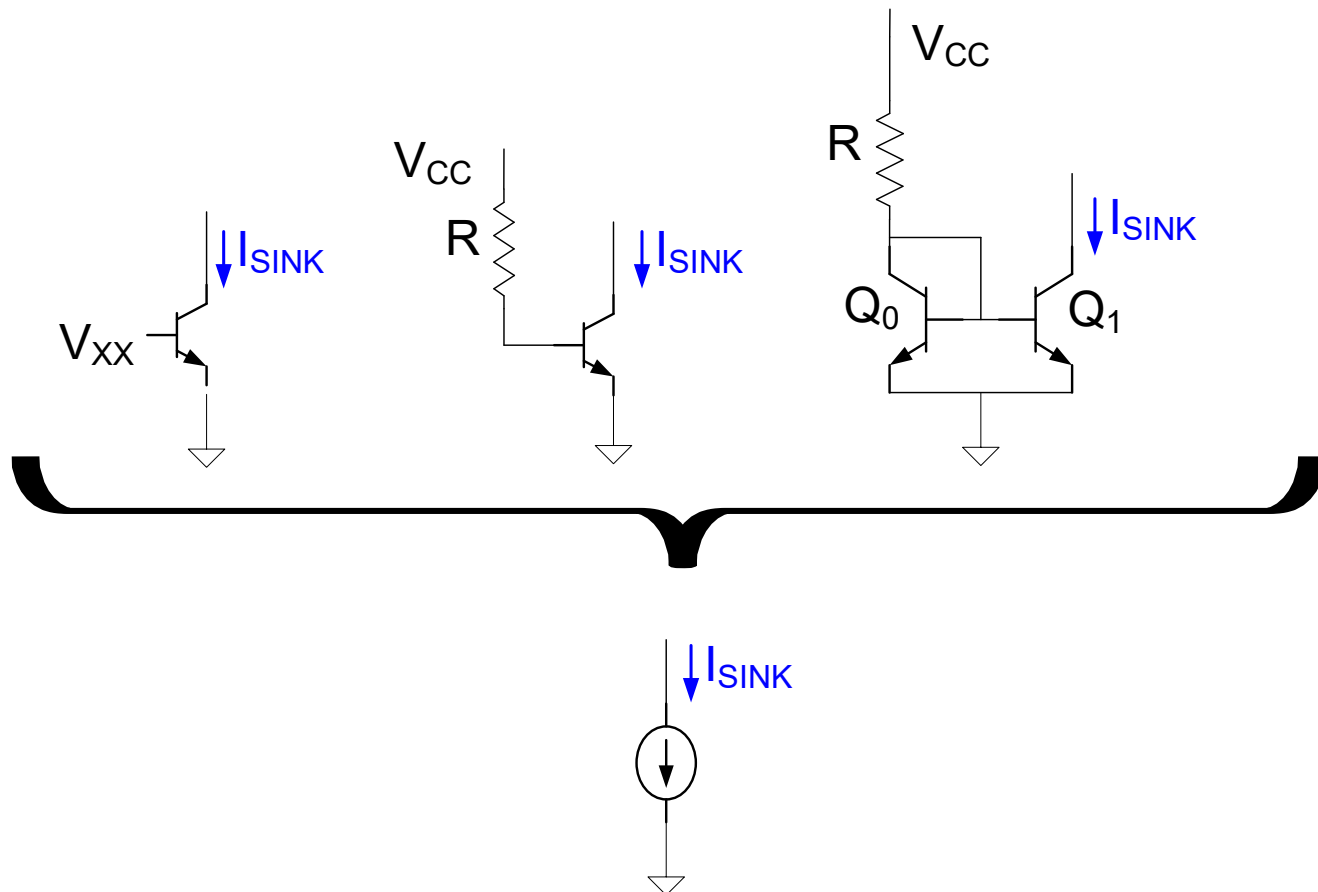
$$A_V \cong -8000$$

→ How can we build the current source?

What is the small-signal model of an actual current source?

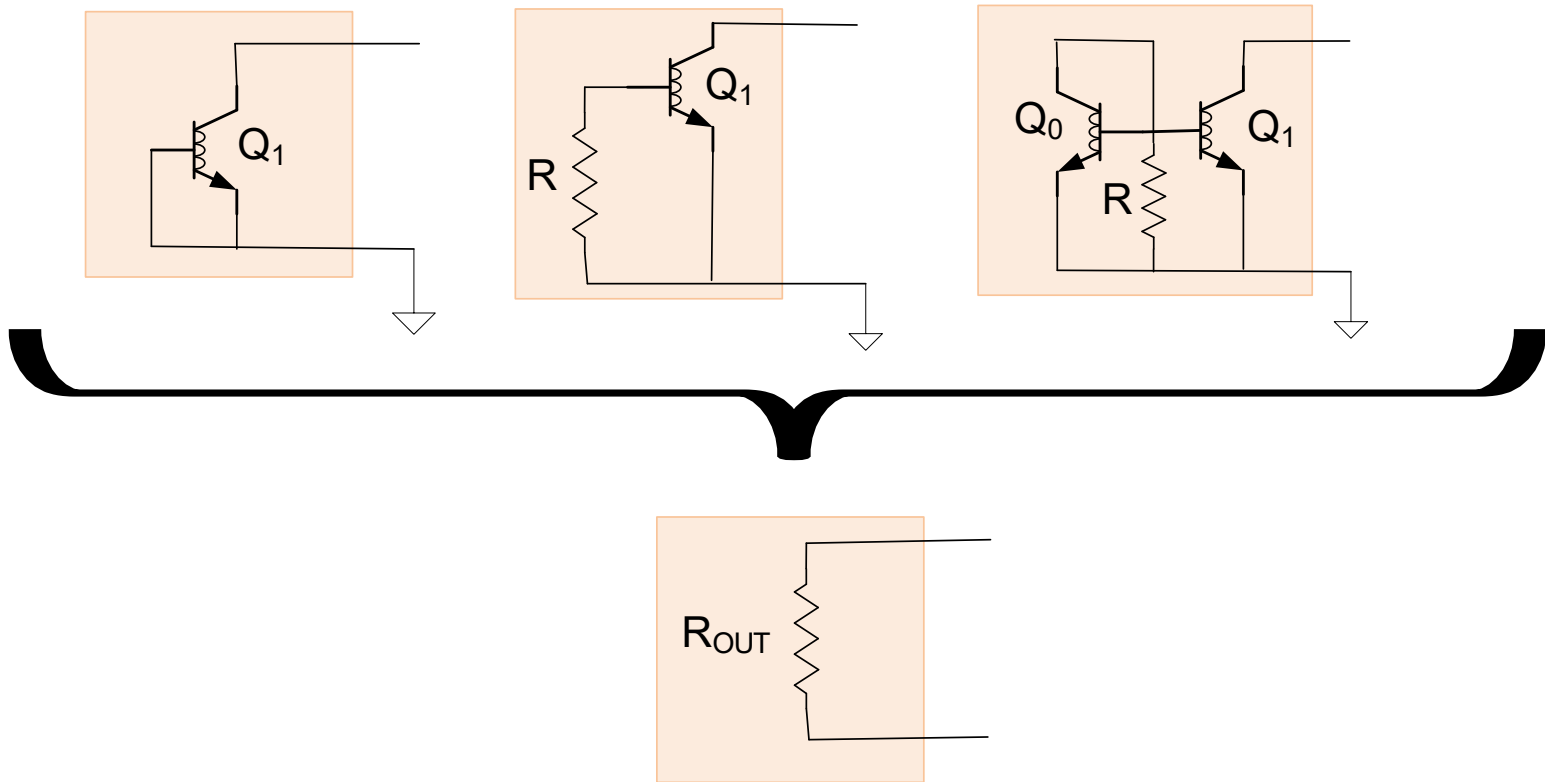
How can we build current source (or sink)?

3 of many ways shown for bipolar process



How can we build current source (or sink)?

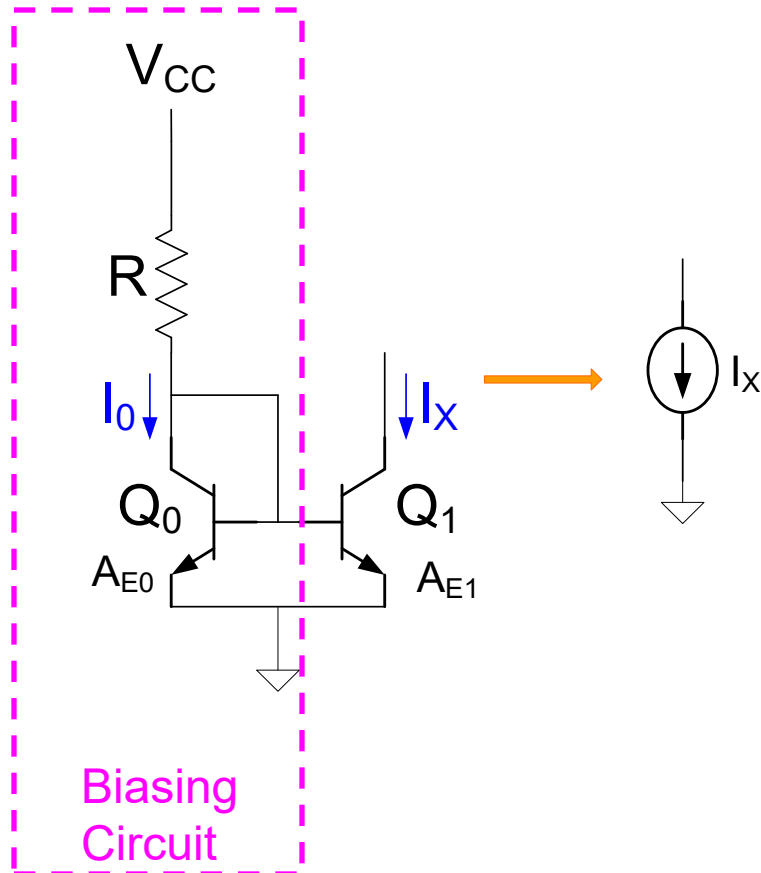
Note: All are small-signal one-ports and equivalent to a resistor R_{OUT}



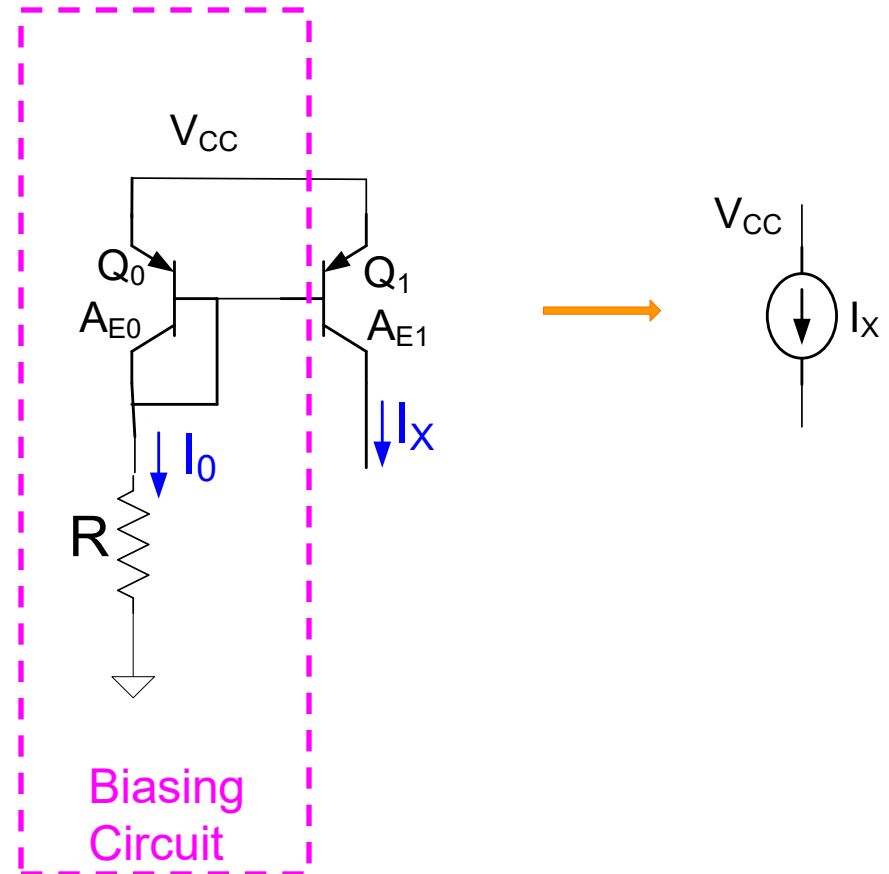
Basic Current Sources and Sinks

Consider as an example:

Bipolar Mirror-Based Current Sink



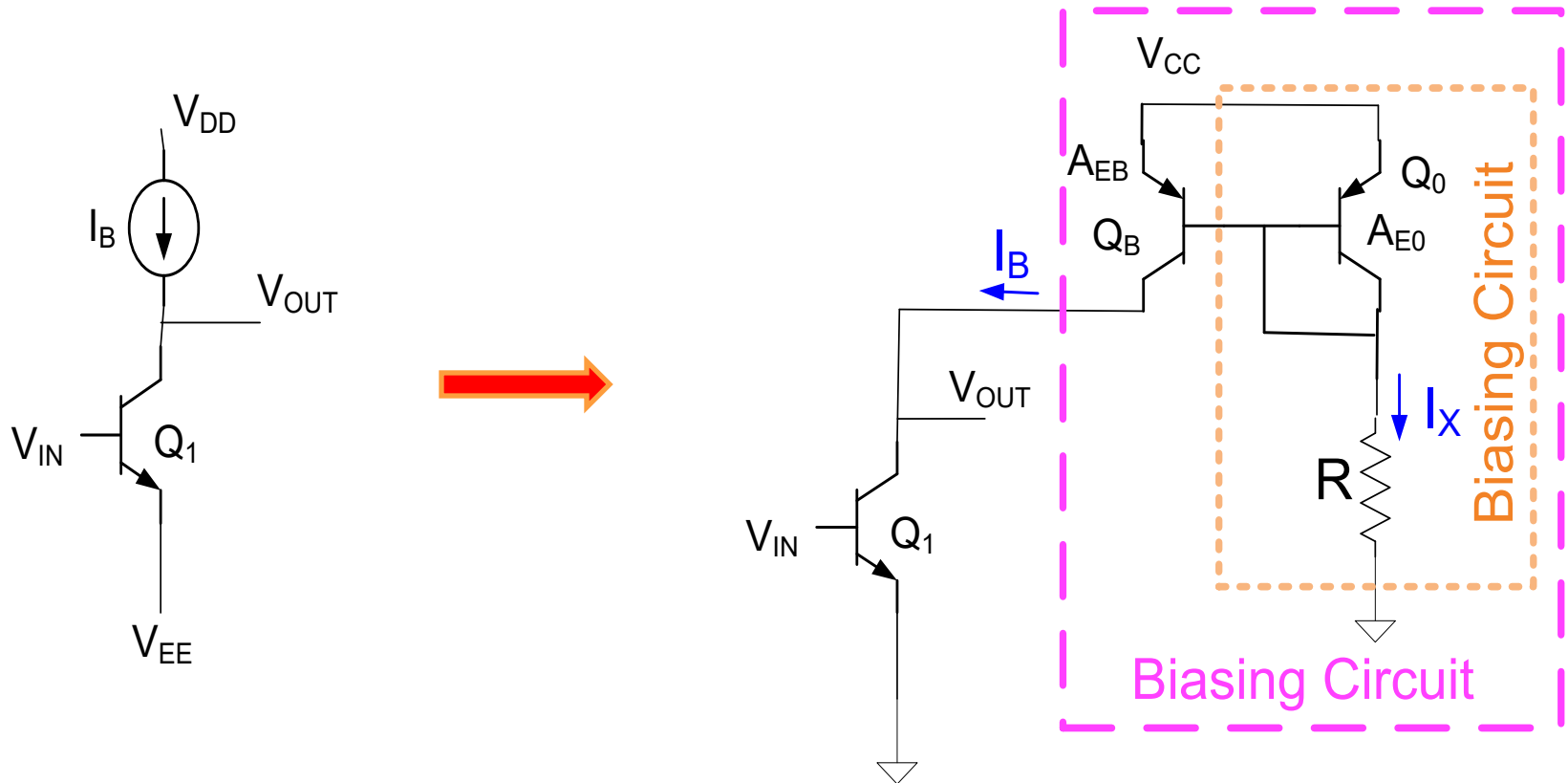
Bipolar Mirror-Based Current Source



Biasing circuit uses same V_{CC} as amplifier and no other independent sources

High-gain amplifier

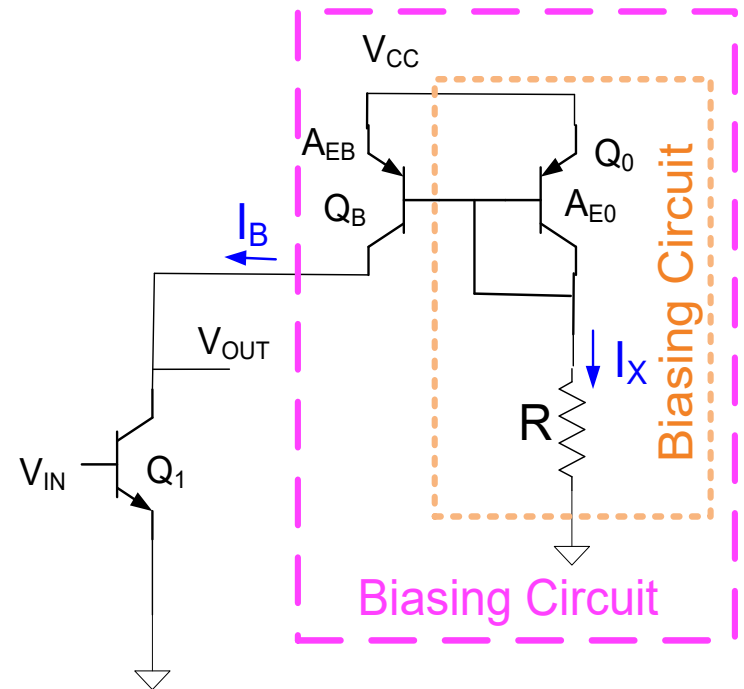
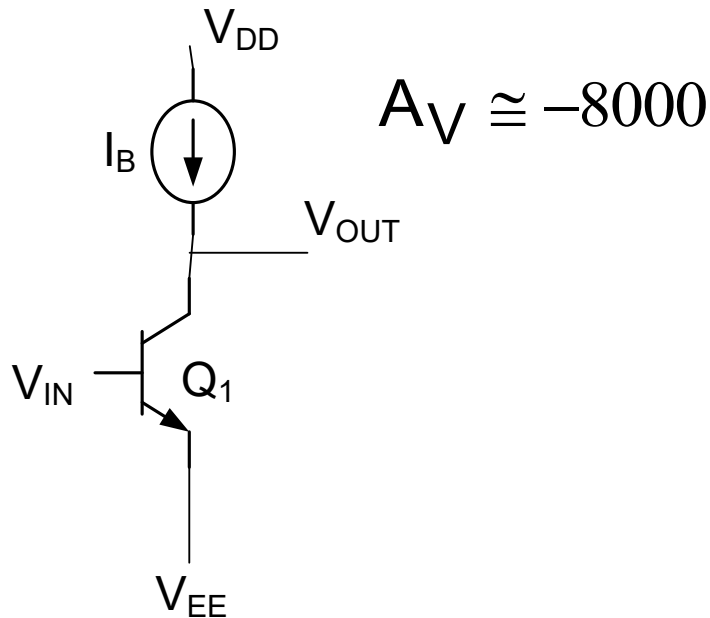
Consider as an example:



- Bias circuitry for biasing circuit requires only a single independent dc voltage source, resistor, and BJT !
- Incremental overhead for each additional current output is only one transistor, Q_B

High-gain amplifier

Consider as an example:



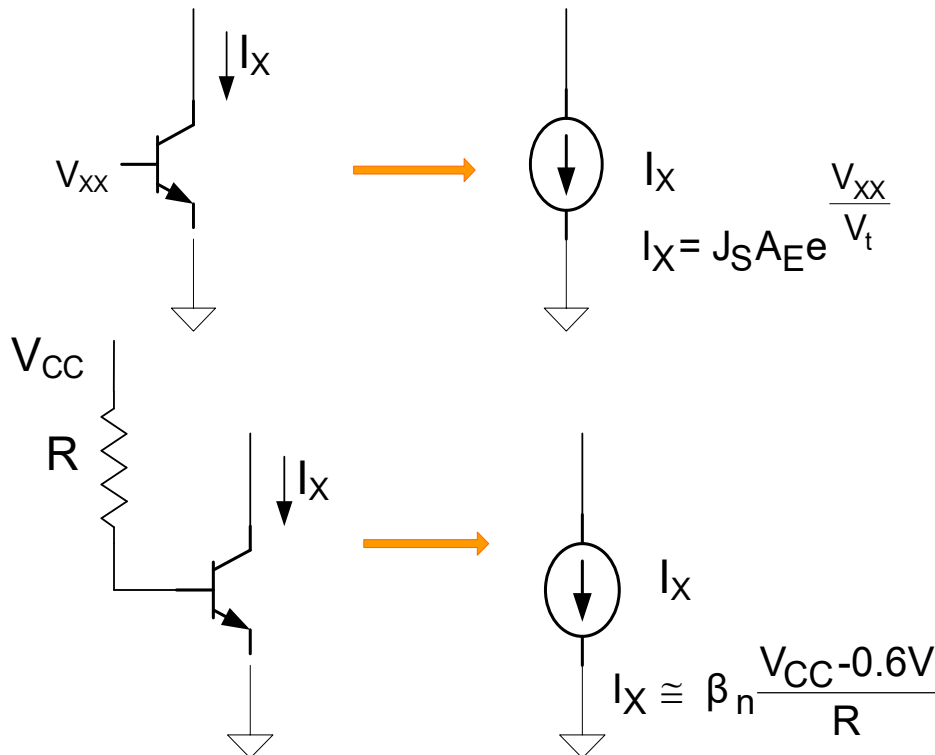
How can we build the current source?

→ What is the small-signal model of an actual current source?

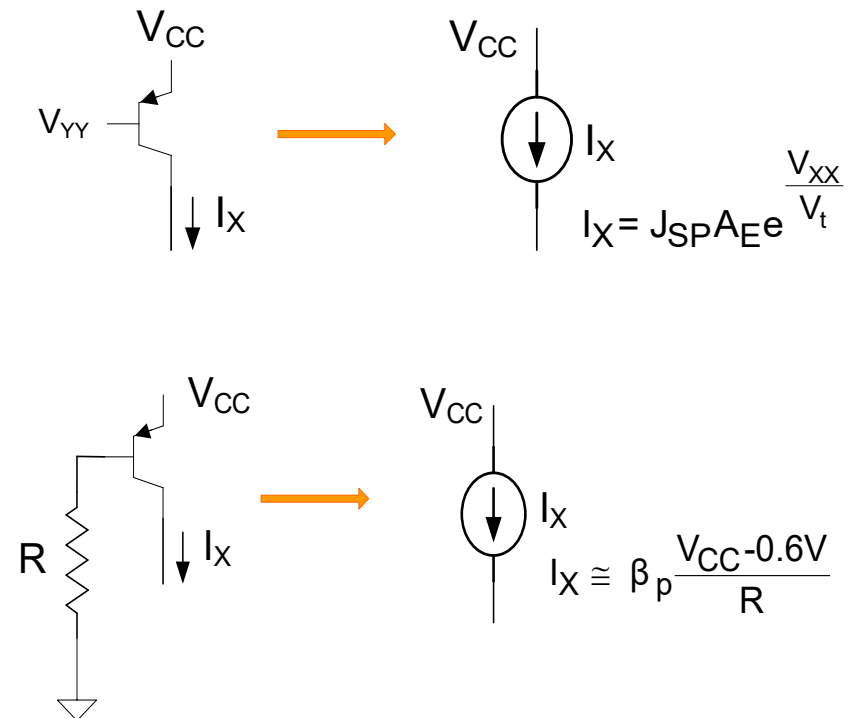
Basic Current Sources and Sinks

DC Models of Basic Bipolar Sinks and Sources

Basic Bipolar Current Sinks



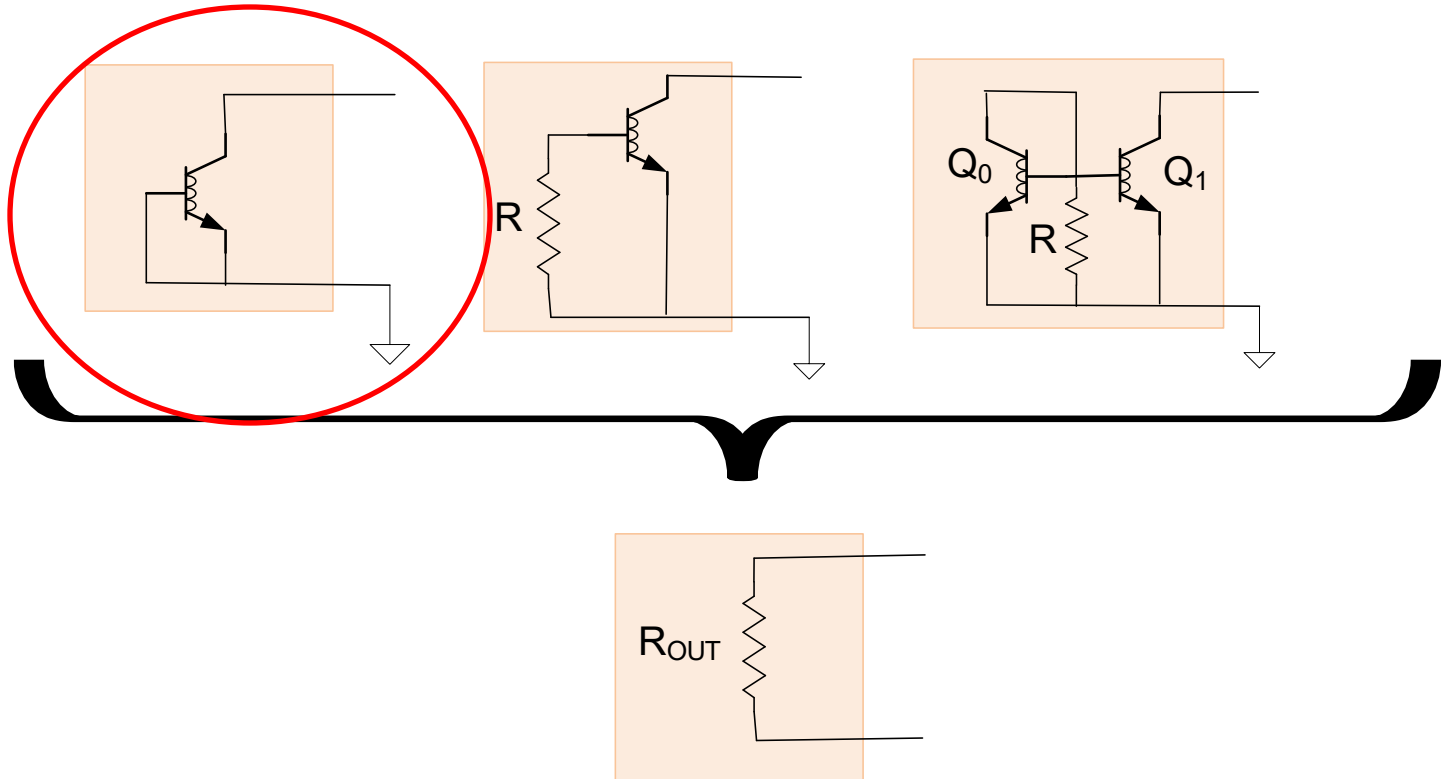
Basic Bipolar Current Sources



- Very practical methods for biasing the BJTs (or MOSFETs) can be used
- Current Mirrors often used for generating sourcing and sinking currents
- Can think of biasing transistors with V_{XX} and V_{YY} in these current sources

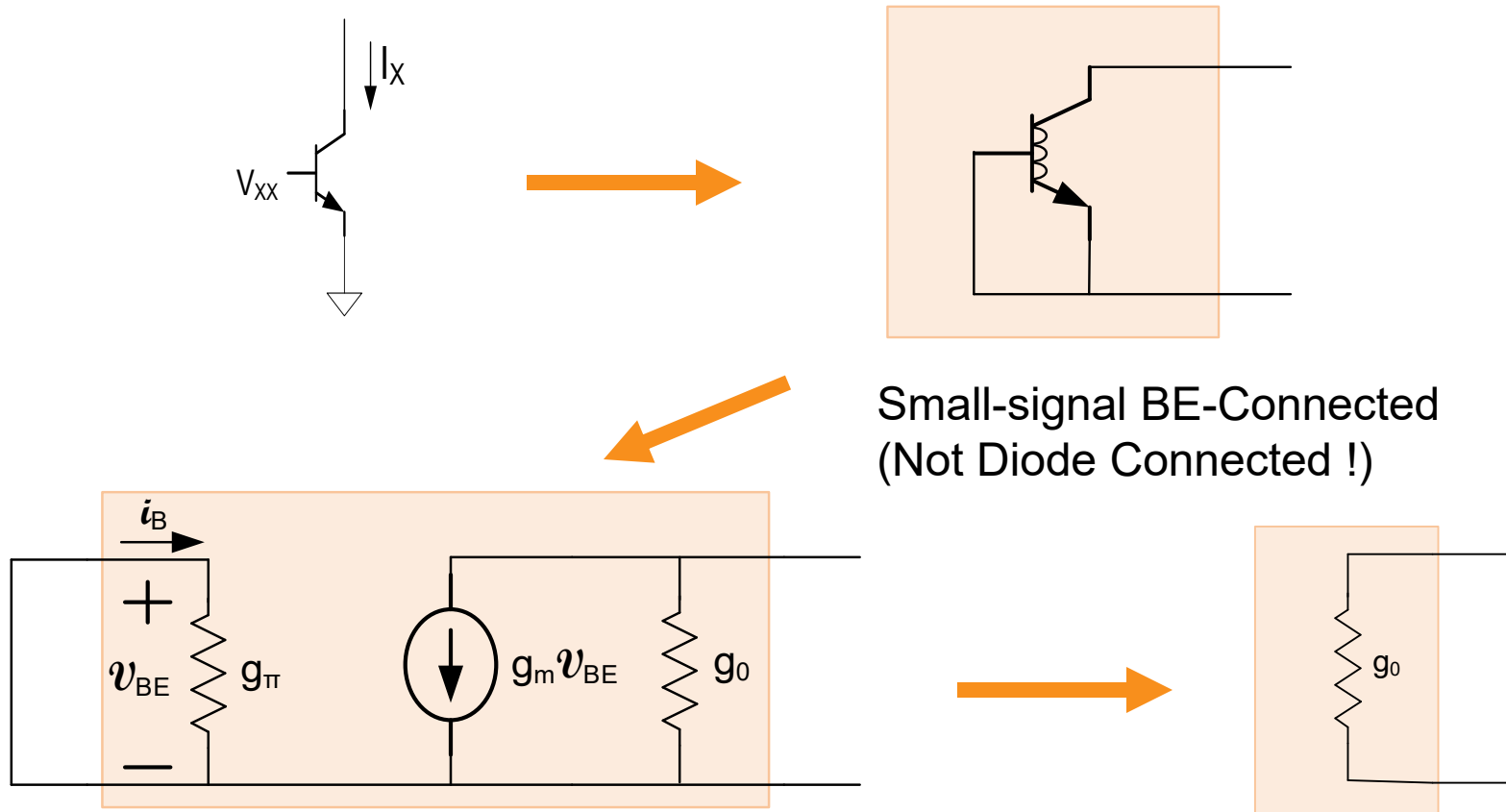
Basic Current Sources and Sinks

Small-signal Model of BJT Current Sinks and Sources



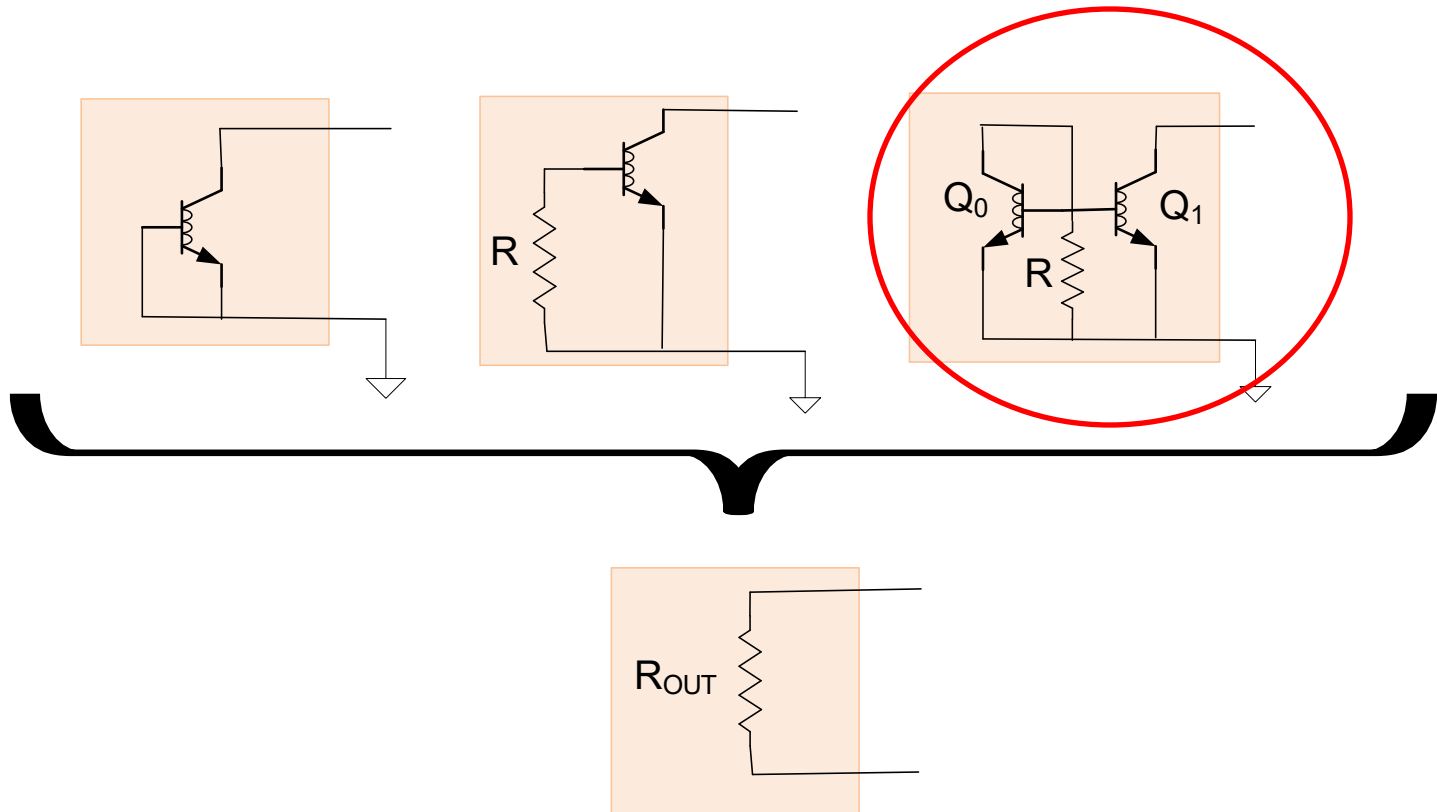
Basic Current Sources and Sinks

Small-signal Model of BJT Current Sinks and Sources



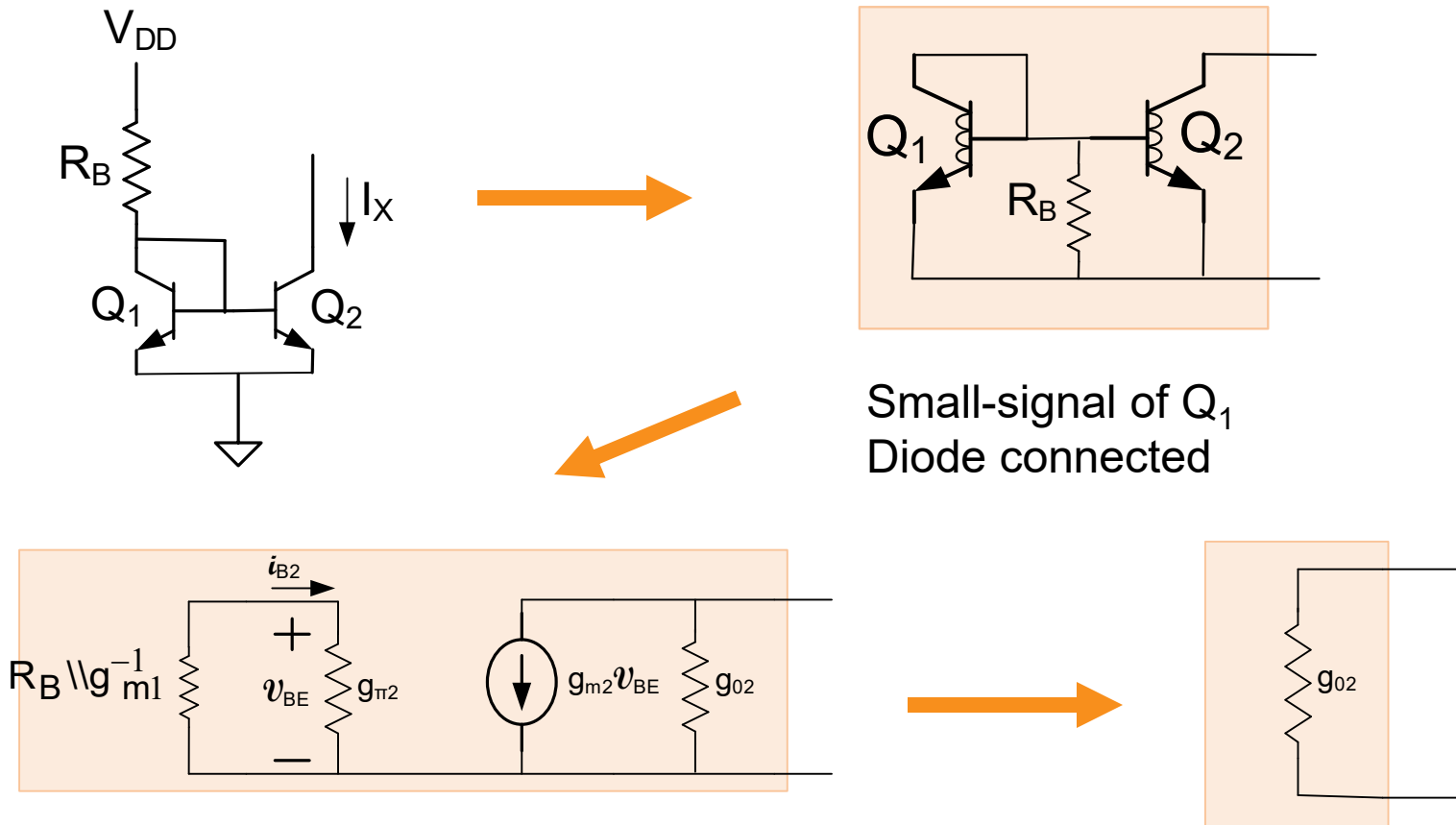
Basic Current Sources and Sinks

Small-signal Model of BJT Current Sinks and Sources



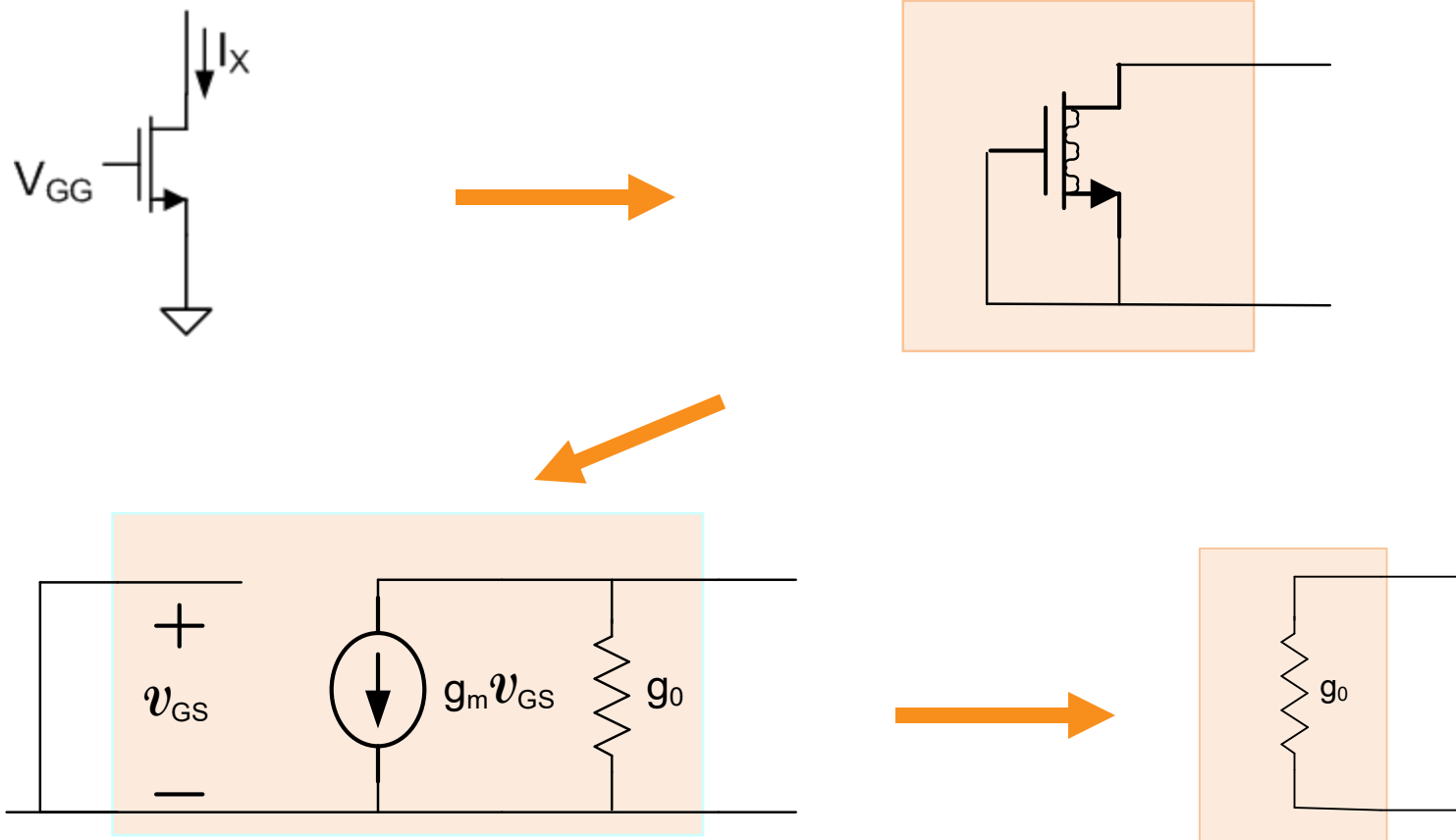
Basic Current Sources and Sinks

Small-signal Model of BJT Current Sinks and Sources



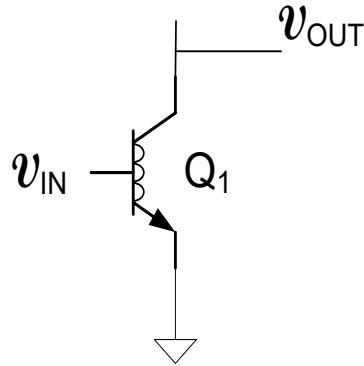
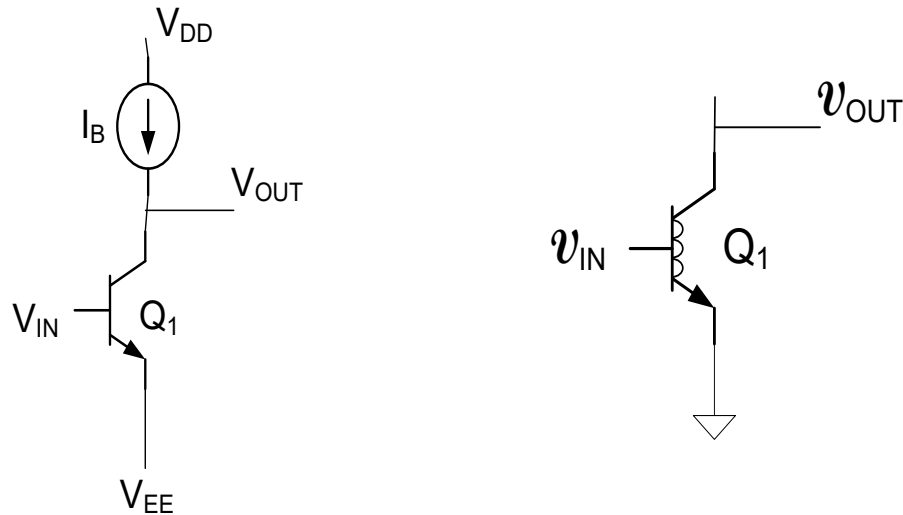
Basic Current Sources and Sinks

Small-signal Model of MOS Current Sinks and Sources

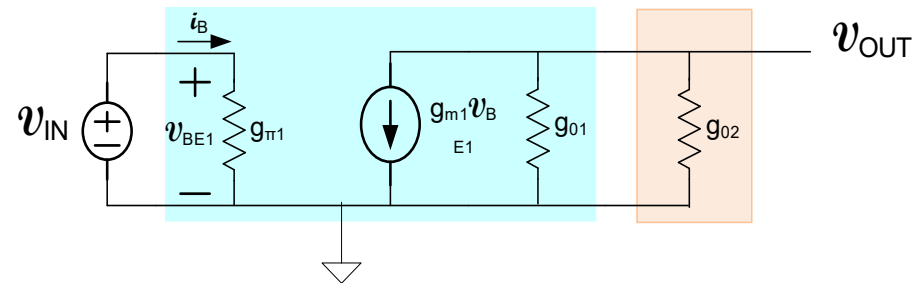
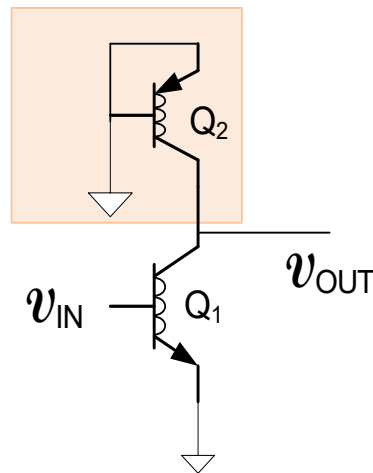
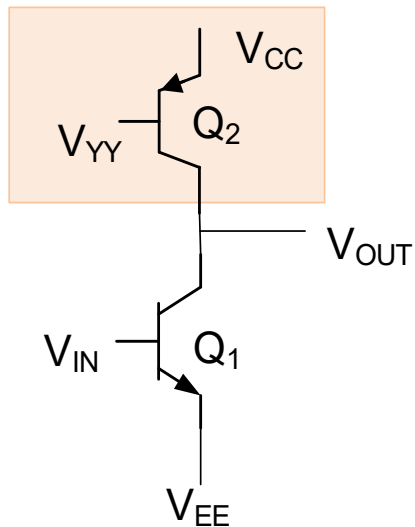


Small-signal model of all other MOS Sinks and Sources introduced thus far are the same

High-gain bipolar amplifier

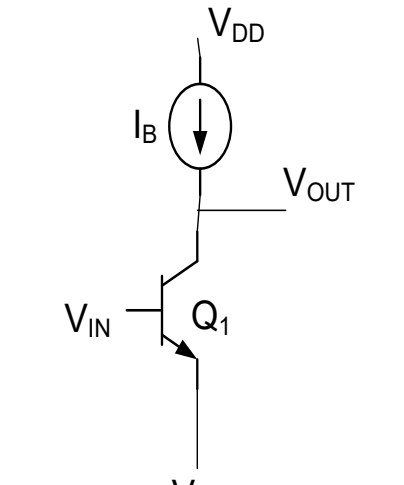


$$A_V = \frac{-g_m}{g_0}$$



$$A_V = \frac{-g_{m1}}{g_{01} + g_{02}} \approx \frac{-g_{m1}}{2g_{01}}$$

High-gain amplifier

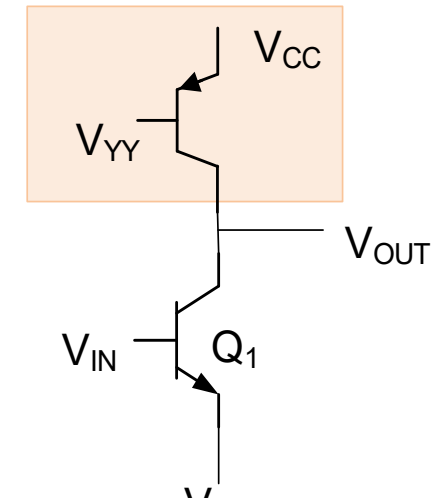


The diagram shows a common-emitter amplifier. The base of the transistor Q_1 is connected to an input voltage V_{IN} . The emitter is connected to a negative supply V_{EE} . The collector is connected to a positive supply V_{DD} through an ideal current source I_B . The output voltage V_{OUT} is taken from the collector.

$$A_V = \frac{-g_m}{g_0}$$

$$= -8000$$

Recall: $\frac{g_m}{g_0} = \frac{g_{m1}}{g_{01}} = \frac{V_{AF}}{V_t} \cong 8000$



The diagram shows a common-emitter amplifier similar to the first one, but with a nonideal current source load. The collector is connected to V_{CC} through a current source that is represented by a dependent current source $g_{m1}V_{YY}$ in parallel with a conductance g_{01} . The output voltage V_{OUT} is taken from the collector. The input V_{IN} is at the base, and the emitter is at V_{EE} .

$$A_V \cong \frac{-g_{m1}}{2g_{01}}$$

$$= -4000$$

- Nonideal current source decreased the gain by a factor of 2
- But the voltage gain is still quite large (-4000)

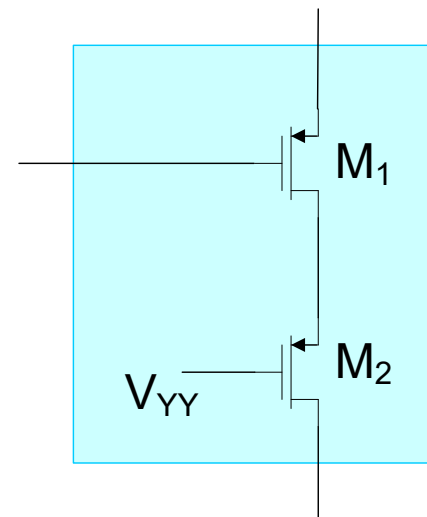
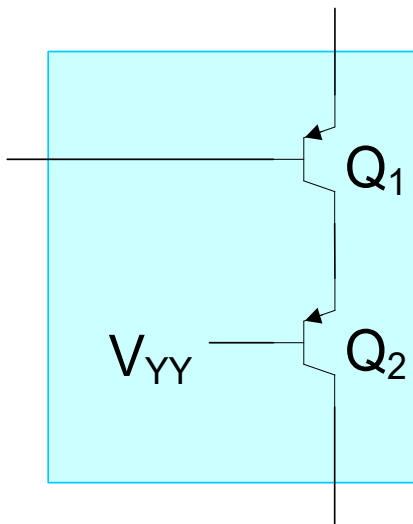
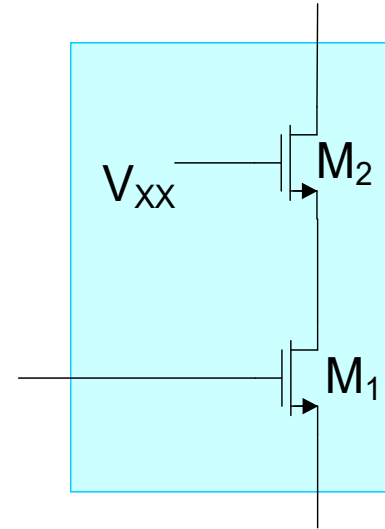
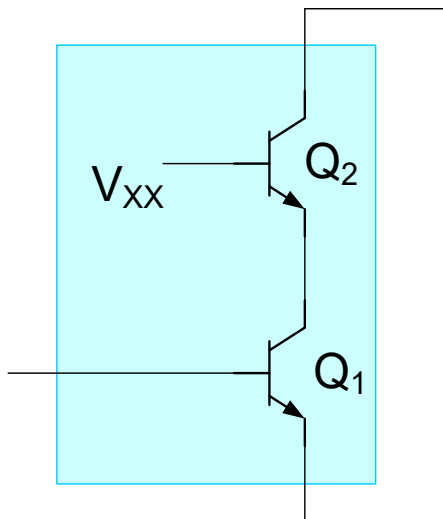
Can the gain be made even larger?

High-gain amplifier

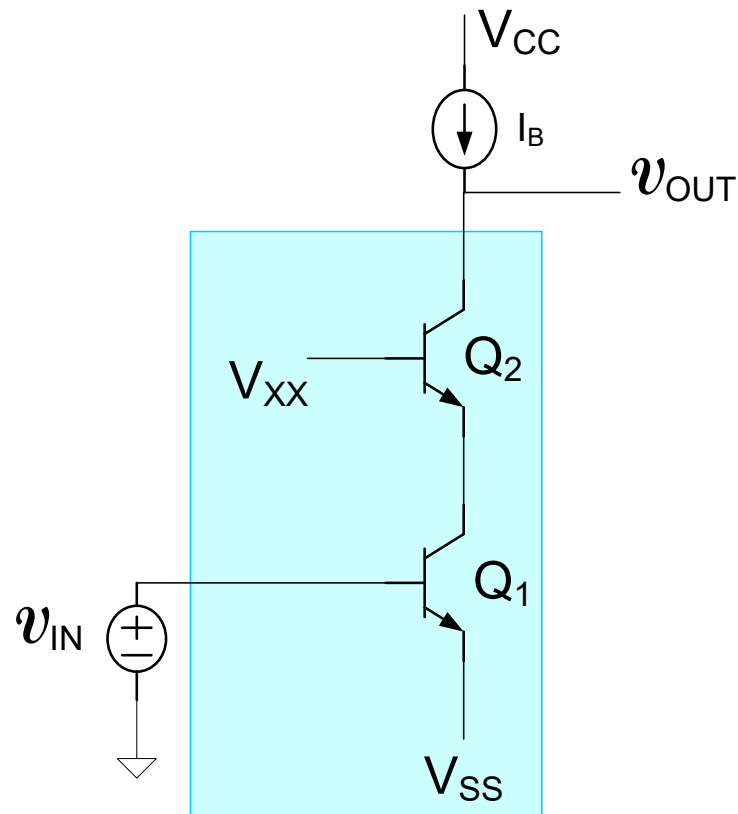
Can the gain be made even larger?

Discuss

The Cascode Configuration



The Cascode Amplifier (consider npn BJT version)



Discuss

- Actually a cascade of a CE stage followed by a CB stage but usually viewed as a “single-stage” structure
- Cascode structure is widely used

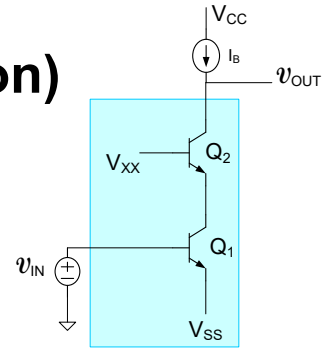
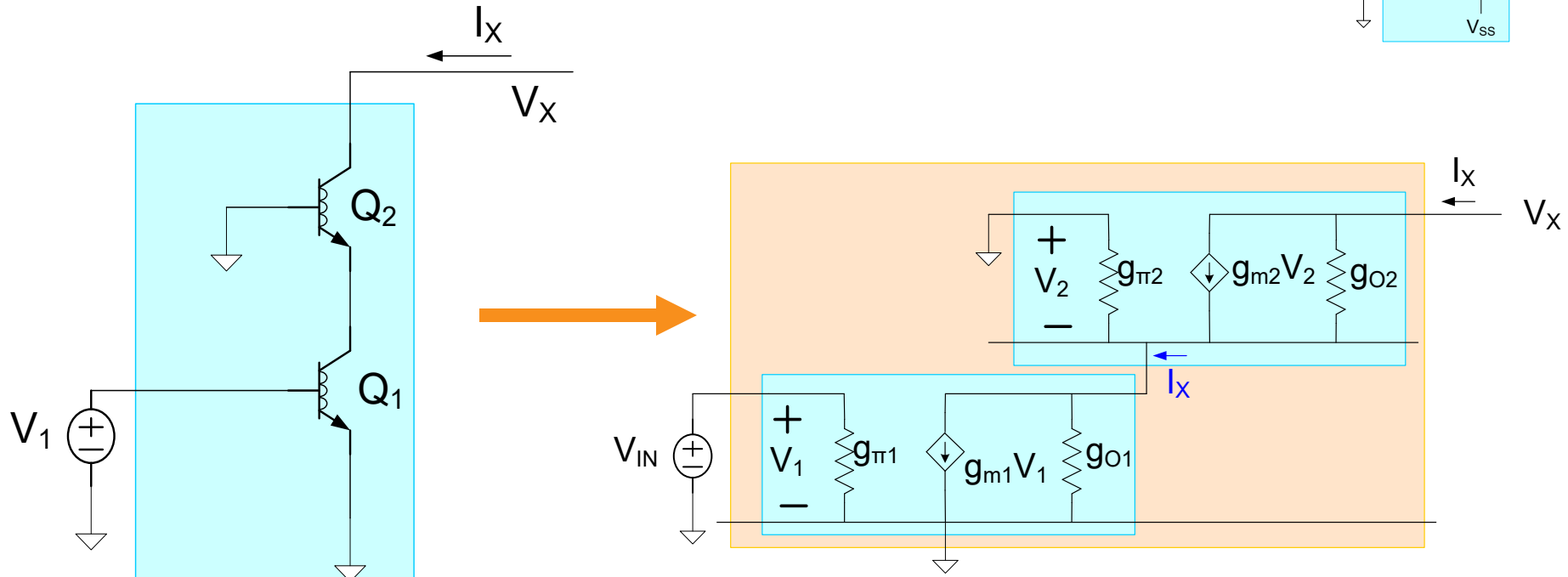
Basic Amplifier Structures

Discuss

1. Common Emitter/Common Source
2. Common Collector/Common Drain
3. Common Base/Common Gate
4. Common Emitter with R_E / Common Source with R_S
- 5. Cascode (actually CE:CB or CS:CD cascade)
6. Darlington (special CE:CE or CS:CS cascade)

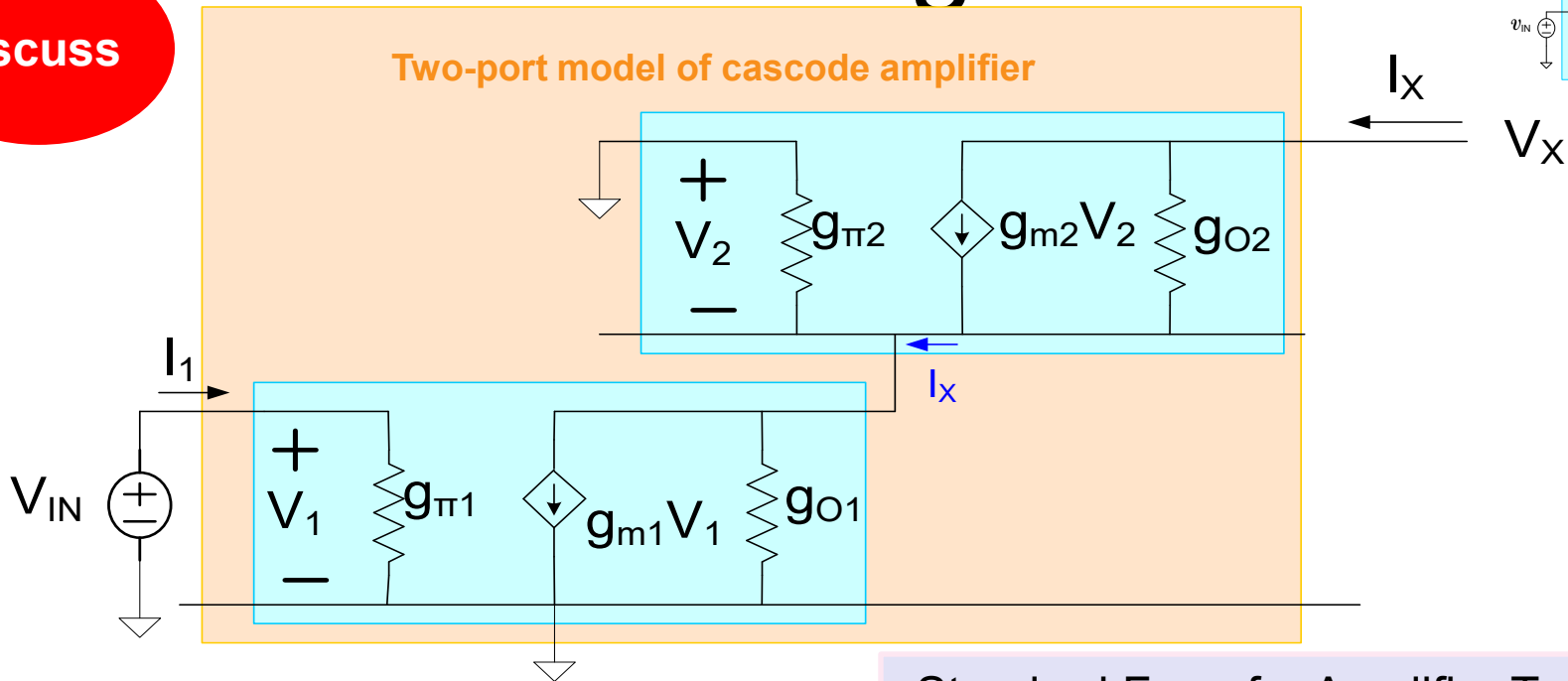
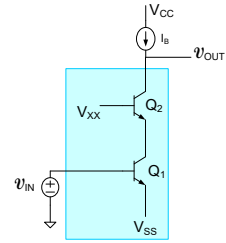
The first 4 are most popular

The Cascode Amplifier (consider npn BJT version)



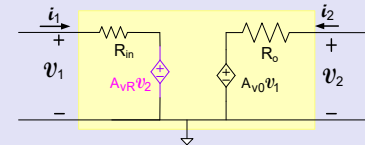
Cascode Configuration

Discuss



$$\left. \begin{aligned} (V_X + V_2)g_{o2} + V_2g_{m2} &= I_X \\ V_1g_{m1} - V_2(g_{o1} + g_{\pi2}) &= I_X \end{aligned} \right\}$$

Standard Form for Amplifier Two-Port



$$\begin{aligned} v_1 &= i_1 R_{IN} + A_{VR} v_2 \\ v_2 &= i_2 R_O + A_{VO} v_1 \end{aligned}$$

Observing $V_1 = V_{IN}$ and eliminating V_2 between these two equations, we obtain

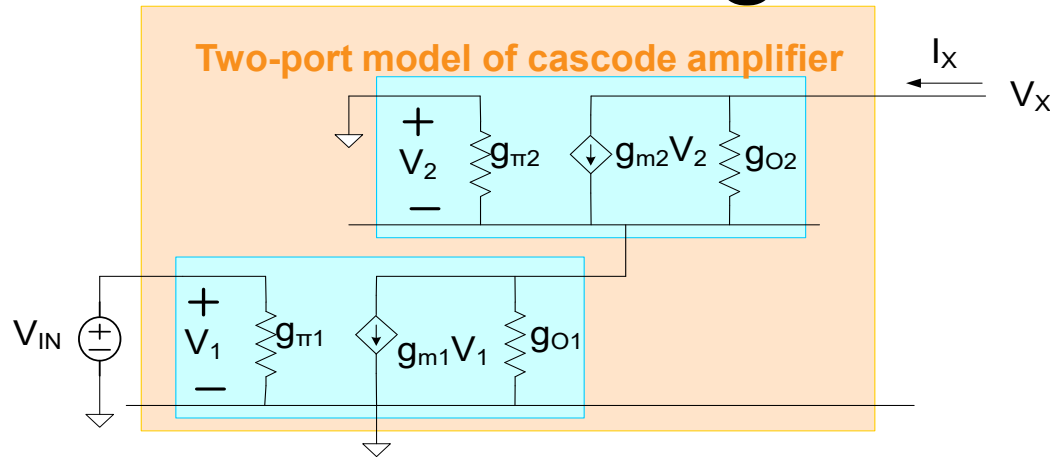
$$V_{IN} = I_1 \cdot \frac{1}{g_{\pi1}}$$

and

$$V_X = I_X \cdot \left[\frac{g_{o1} + g_{o2} + g_{\pi2} + g_{m2}}{g_{o2}(g_{o1} + g_{\pi2})} \right] - V_{IN} \cdot \left[\frac{g_{m1}(g_{o2} + g_{m2})}{g_{o2}(g_{\pi2} + g_{o1})} \right]$$

Cascode Configuration

Discuss



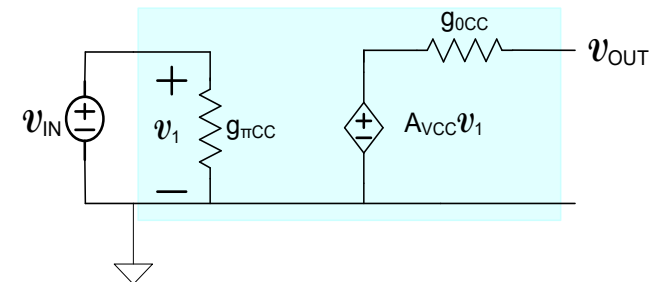
$$V_X = I_X \cdot \left[\frac{g_{o1} + g_{o2} + g_{\pi 2} + g_{m2}}{g_{o2}(g_{o1} + g_{\pi 2})} \right] - V_{IN} \cdot \left[\frac{g_{m1}(g_{o2} + g_{m2})}{g_{o2}(g_{\pi 2} + g_{o1})} \right]$$

$$V_{IN} = I_1 \cdot \frac{1}{g_{\pi 1}}$$

It thus follows for the npn bipolar structure that it is unilateral and :

$$A_{VCC} = - \left[\frac{g_{m1}(g_{o2} + g_{m2})}{g_{o2}(g_{\pi 2} + g_{o1})} \right] \cong - \left[\frac{g_{m1}g_{m2}}{g_{o2}g_{\pi 2}} \right]$$

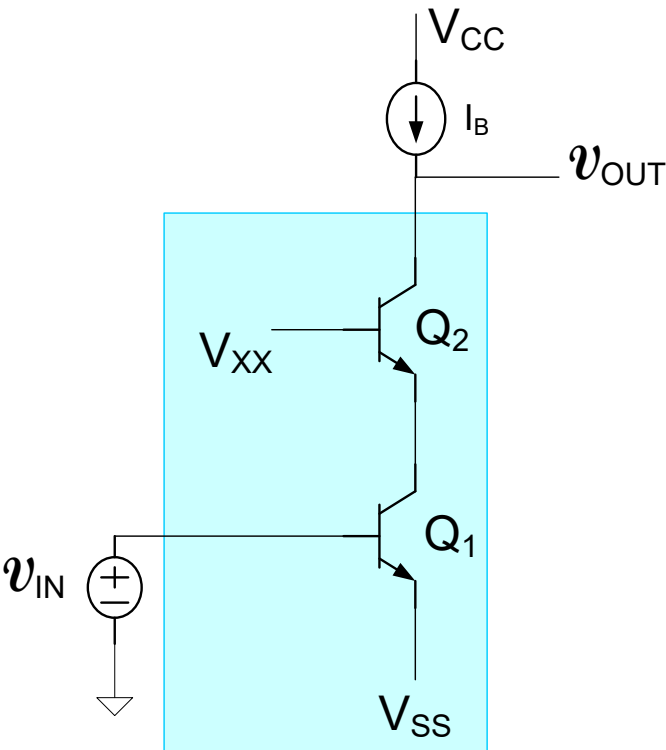
$$g_{oCC} = \left[\frac{g_{o2}(g_{o1} + g_{\pi 2})}{g_{o1} + g_{o2} + g_{\pi 2} + g_{m2}} \right] \cong \left[\frac{g_{o2}g_{\pi 2}}{g_{m2}} \right]$$



$$g_{\pi CC} = g_{\pi 1}$$

Cascode Configuration

Discuss



$$A_{V_{CC}} \cong - \left[\frac{g_{m1} g_{m2}}{g_{o2} g_{\pi 2}} \right]$$

$$g_{oCC} \cong \left[\frac{g_{o2} g_{\pi 2}}{g_{m2}} \right]$$

$$g_{\pi CC} = g_{\pi 1}$$

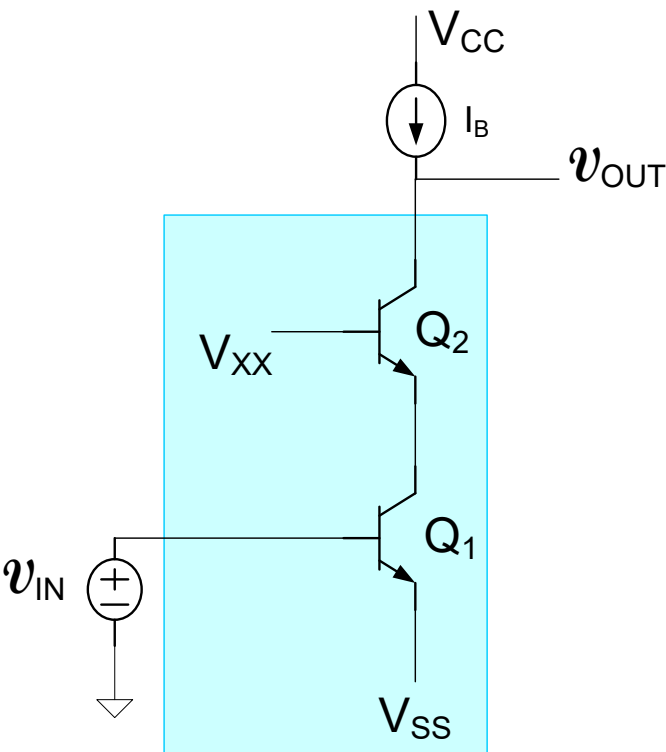
$$A_{V_{CC}} \cong - \left[\frac{g_{m1}}{g_{o2}} \beta \right] \cong - \left[\frac{g_{m1}}{g_{o1}} \right] \beta$$

$$g_{oCC} \cong \frac{g_{o1}}{\beta}$$

- Voltage gain is a factor of β larger than that of the CE amplifier with current source load
- Output impedance is a factor of β larger than that of the CE amplifier

Cascode Configuration

Discuss



$$A_{V_{CC}} \cong - \left[\frac{g_{m1}}{g_{02}} \beta \right] \cong - \left[\frac{g_{m1}}{g_{01}} \right] \beta$$

$$g_{0CC} \cong \frac{g_{02}}{\beta}$$

In the MPOP domain:

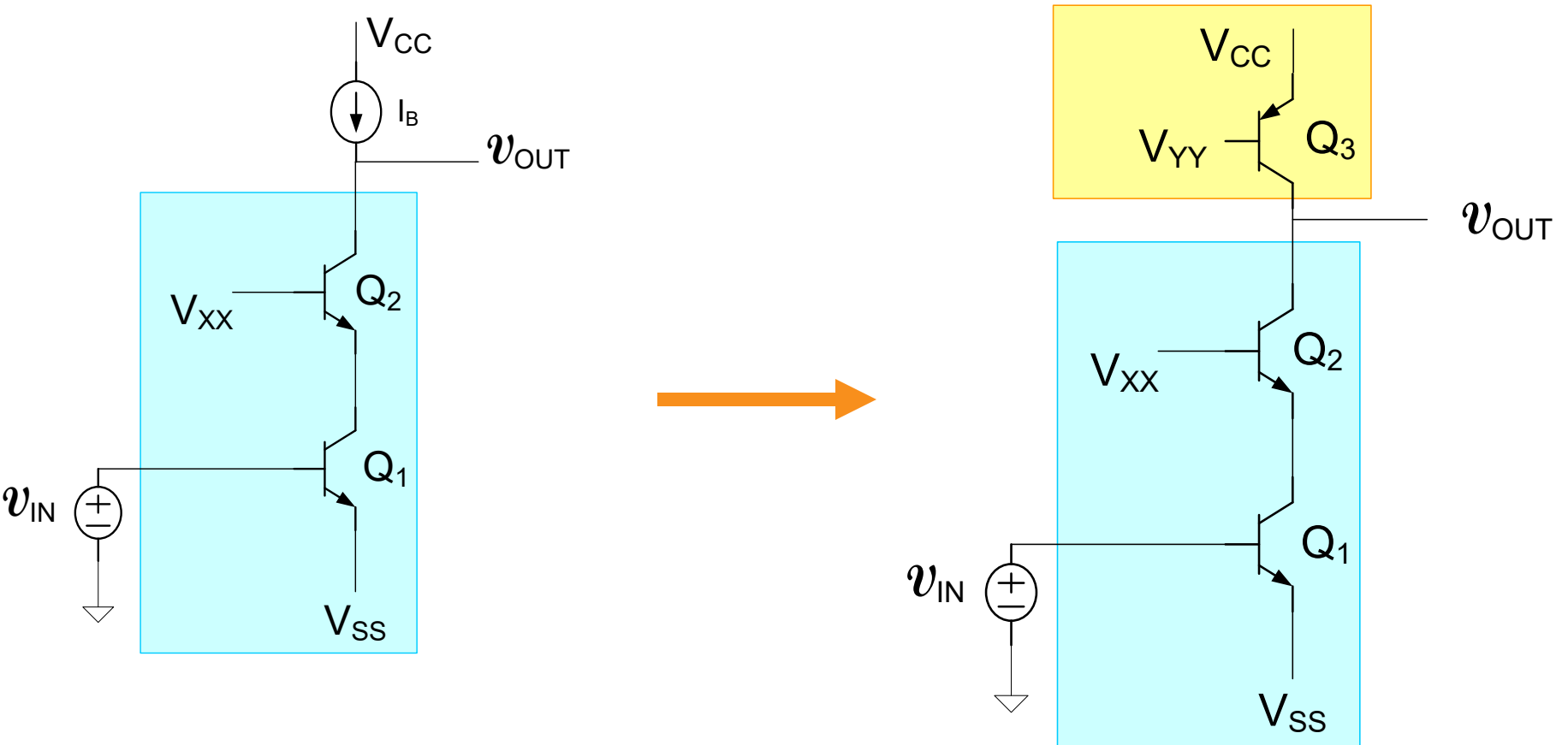
$$A_{V_{CC}} \cong - \left[\frac{g_{m1}}{g_{01}} \right] \beta = \left[\frac{2V_{AF}}{V_t} \right] \beta = [-8000]100$$

$$A_{V_{CC}} \cong -800,000$$

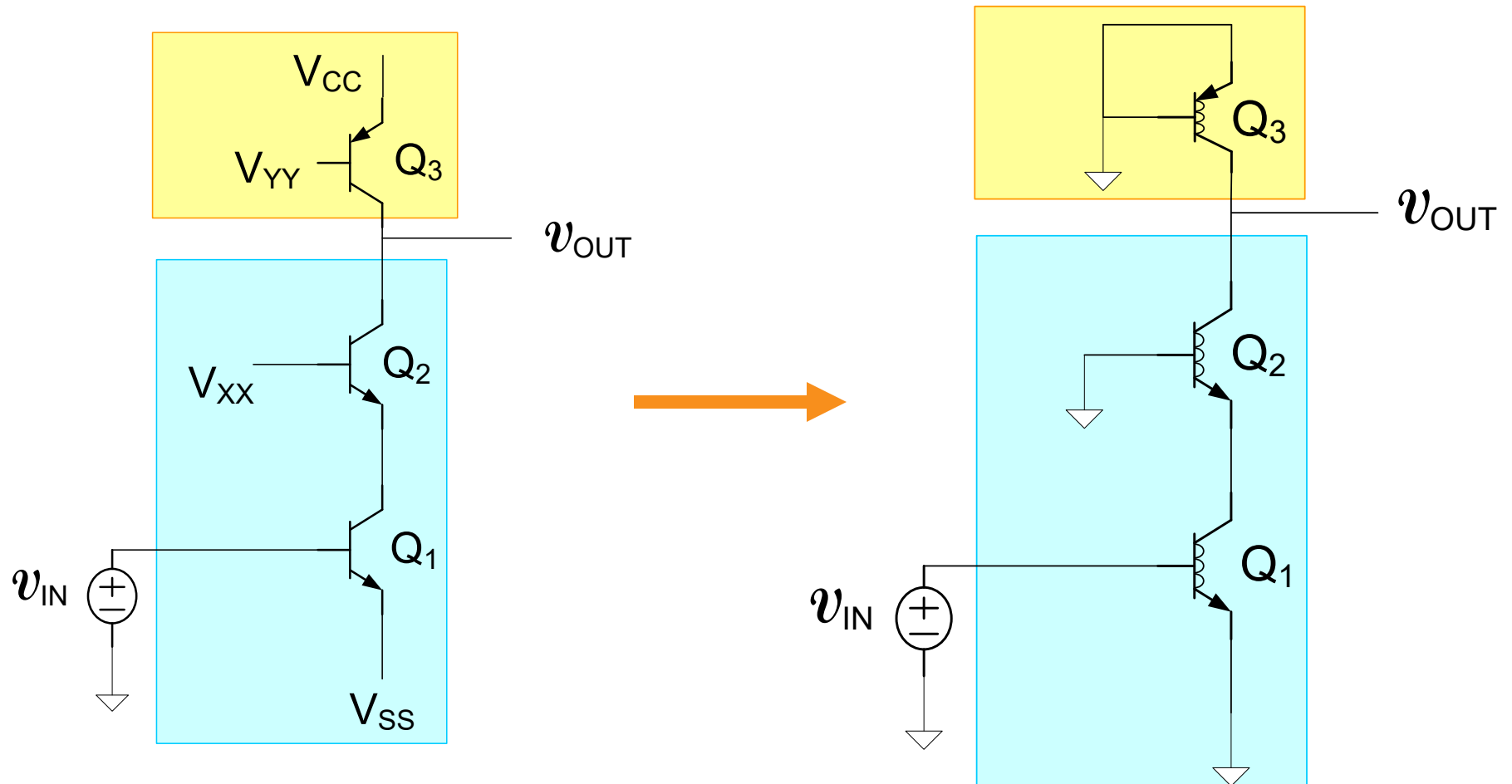
This gain is very large and only requires two transistors!

What happens to the gain if a transistor-level current source is used for I_B ?

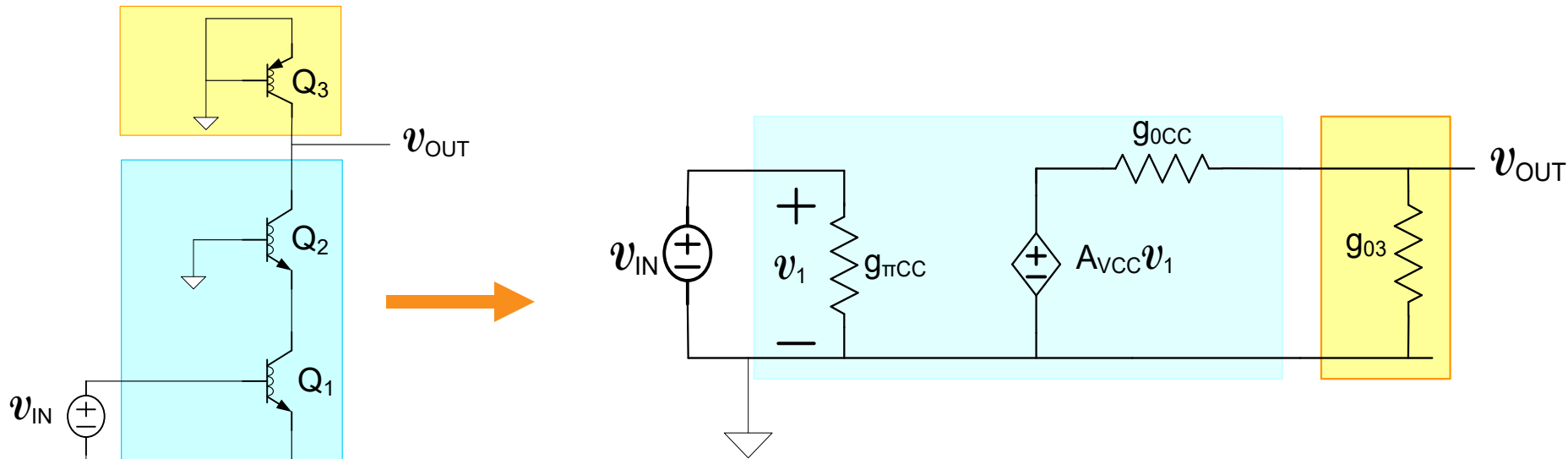
Cascode Configuration



Cascode Configuration



High-gain amplifier comparisons



It thus follows that

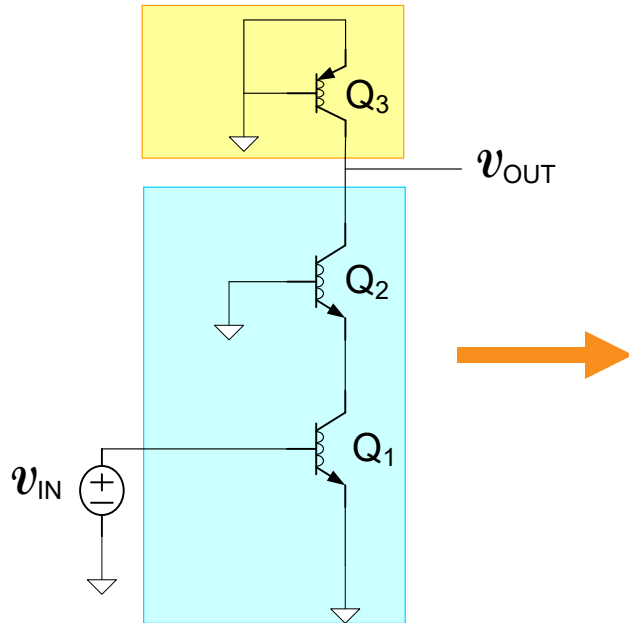
$$A_V = A_{VCC} \left[\frac{g_{0CC}}{g_{03} + g_{0CC}} \right]$$

But $g_{0CC} \simeq g_{01}/\beta = g_{03}/\beta$

$$A_V \simeq A_{VCC} \left[\frac{g_{0CC}}{g_{03}} \right] \simeq \frac{A_{VCC}}{\beta}$$

This is a dramatic reduction in gain compared to what the ideal current source biasing provided

Cascode Configuration



$$A_V \cong A_{VCC} \left[\frac{g_{0CC}}{g_{03}} \right] \cong \frac{A_{VCC}}{\beta}$$

But recall

$$A_{VCC} \cong - \left[\frac{g_{m1}}{g_{01}} \right] \beta$$

Thus
$$A_V \cong - \left[\frac{g_{m1}}{g_{01}} \right]$$

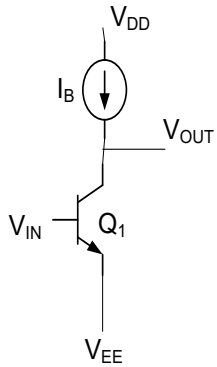
In the MPOP domain:

$$A_V \cong - \left[\frac{I_{CQ} / V_t}{I_{CQ} / V_{AF}} \right] = - \left[\frac{V_{AF}}{V_t} \right] \cong -8000$$

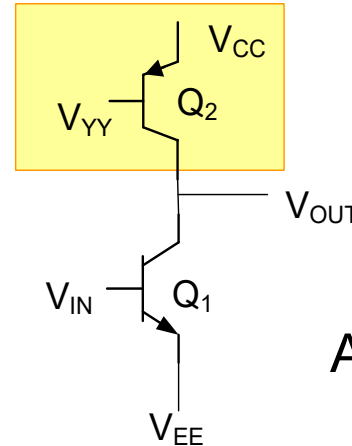
- This is still a factor of 2 better than that of the CE amplifier with transistor current source $\left(A_{VCE} \cong - \left[\frac{g_{m1}}{2g_{01}} \right] \right)$

- It only requires one additional transistor
- But its not nearly as good as the gain the cascode circuit seemed to provide

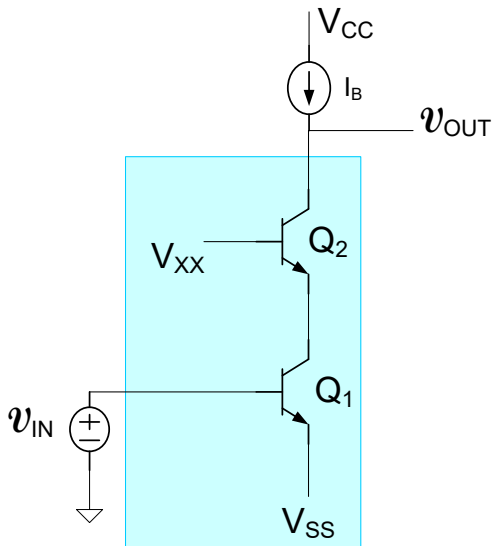
Cascode Configuration Comparisons



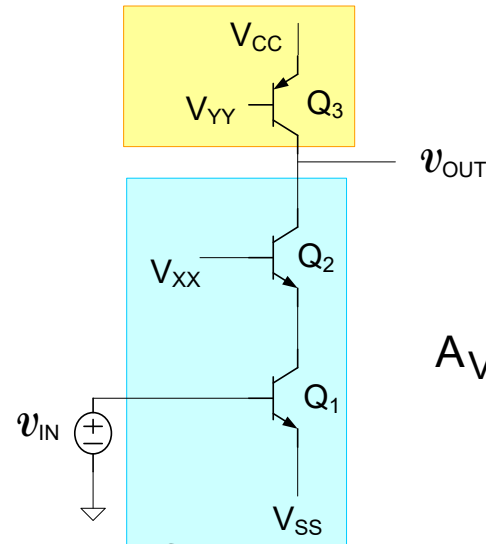
$$A_V = \frac{-g_m}{g_0}$$



$$A_V \cong \frac{-g_{m1}}{g_{01} + g_{02}} = \frac{-g_{m1}}{2g_{01}}$$



$$A_V \cong -\left[\frac{g_{m1}}{g_{01}}\right]\beta$$



$$A_V \cong -\left[\frac{g_{m1}}{\frac{g_{01}}{\beta} + g_{03}}\right] \cong -\left[\frac{g_{m1}}{g_{03}}\right]$$

Gain limited by output impedance of current source !!

Can we design a better current source?

In particular, one with a higher output impedance?

Better current sources

Need a higher output impedance than g_o



The output impedance of the cascode circuit itself was very large !

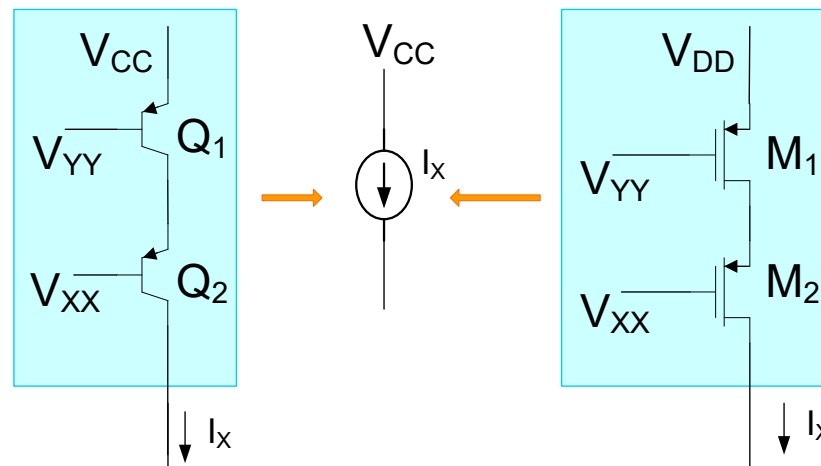
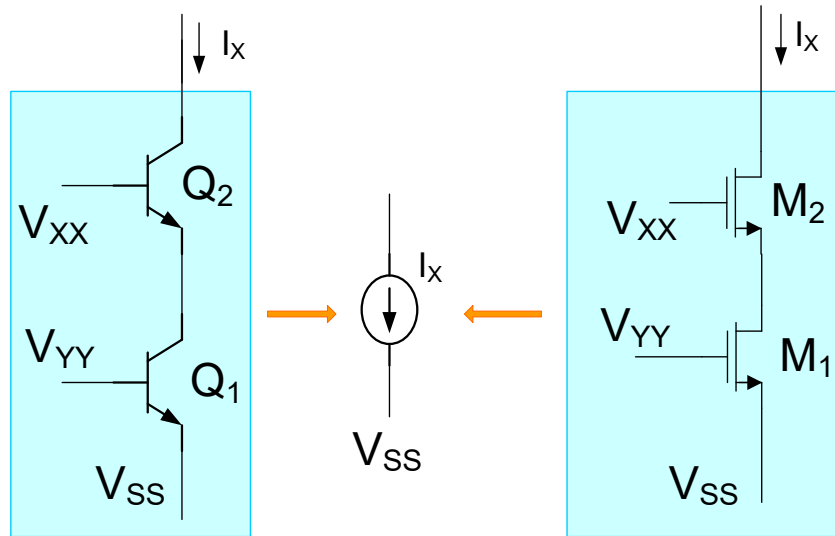
$$g_{oCC} \cong \frac{g_{o1}}{\beta}$$

Can a current source be built with the cascode circuit ?

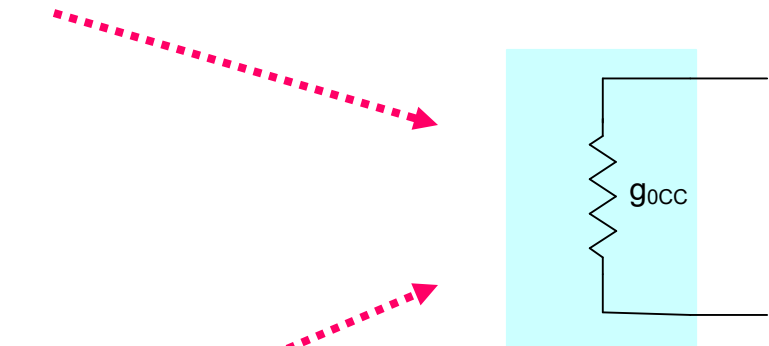
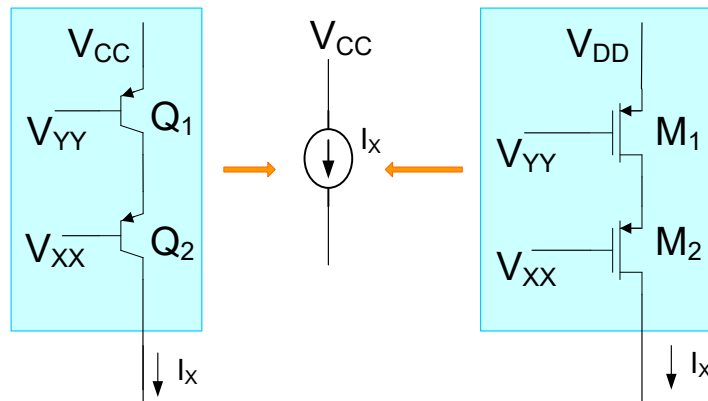
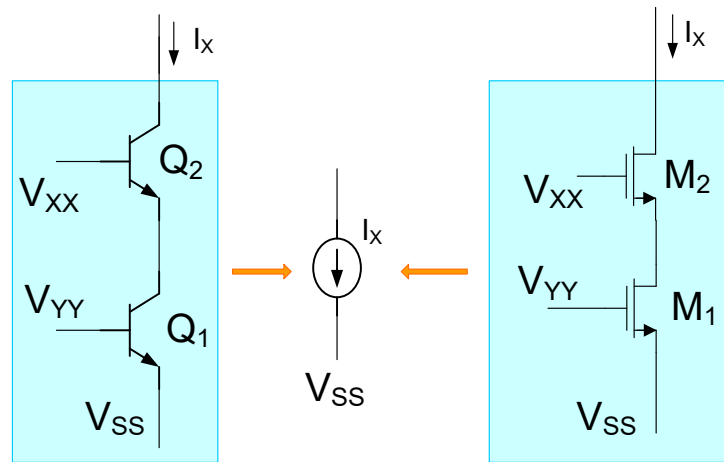
Cascode current sources



Discuss



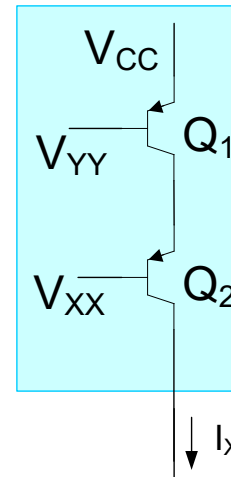
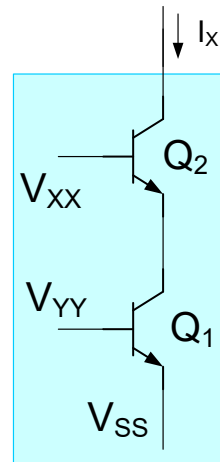
Cascode current sources



All have the same small-signal model

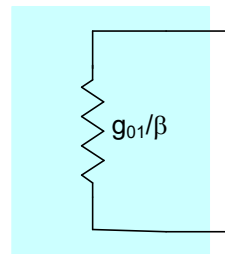
$$g_{0CC} = \left[\frac{g_{02}(g_{01} + g_{\pi 2})}{g_{01} + g_{02} + g_{\pi 2} + g_{m2}} \right]$$

Cascode current sources

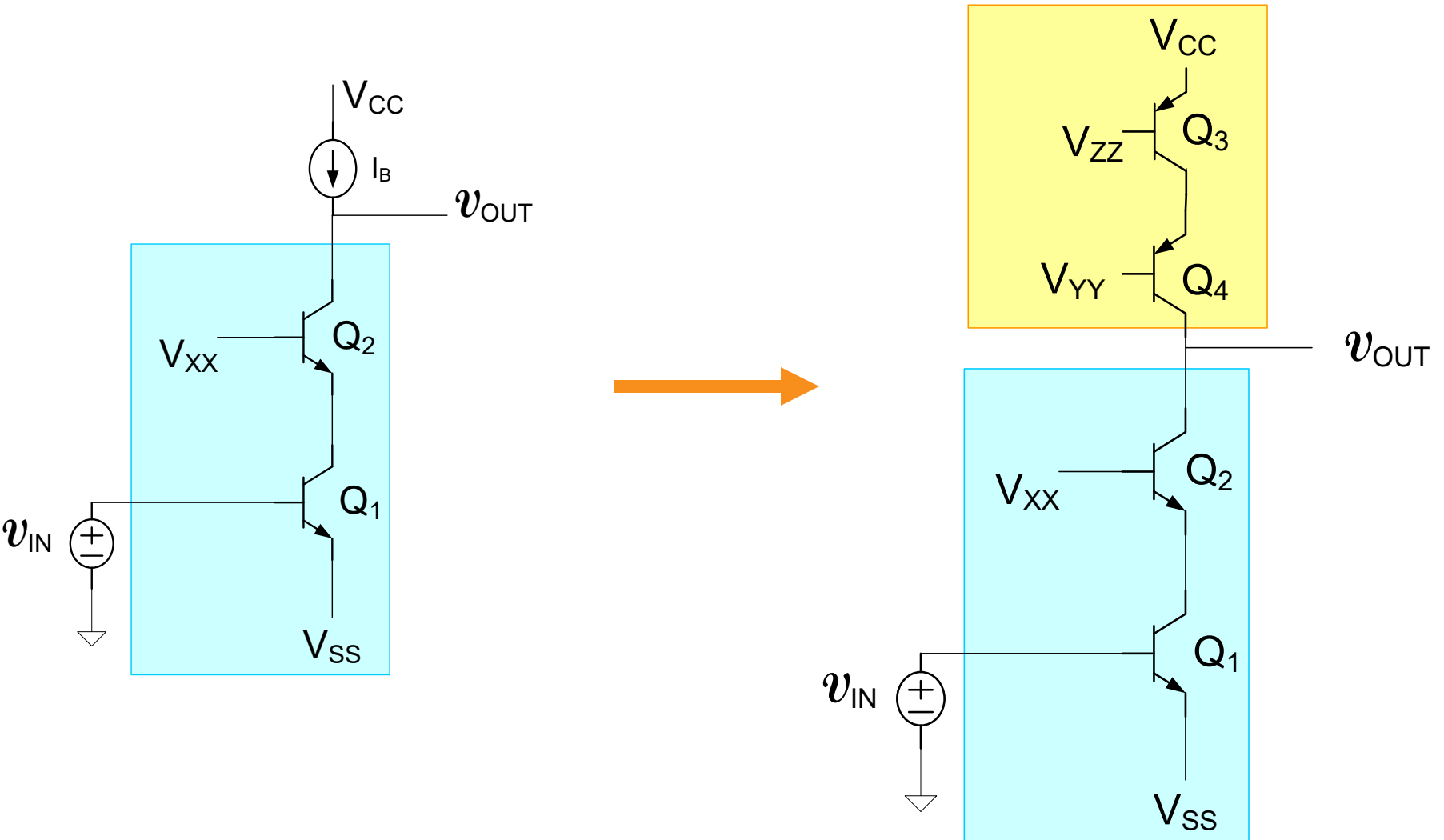


For the BJT cascode current sources

$$g_{oCC} = \left[\frac{g_{o2}(g_{o1} + g_{\pi 2})}{g_{o1} + g_{o2} + g_{\pi 2} + g_{m2}} \right] \cong \left[\frac{g_{o2}g_{\pi 2}}{g_{m2}} \right] = \frac{g_{o1}}{\beta}$$

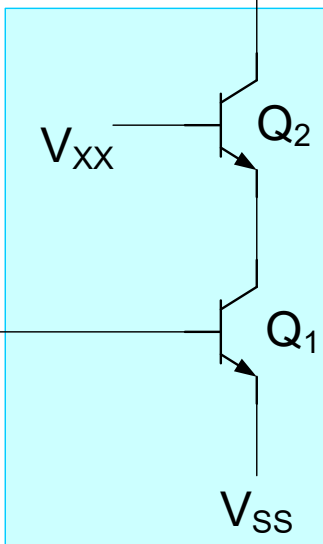
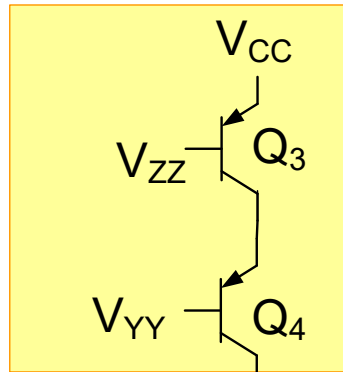


Cascode Configuration



Cascode Configuration

Discuss



$$A_V \cong - \left[\frac{g_{m1}}{\frac{g_{o1}}{\beta_1} + g_{oCC}} \right] \cong - \left[\frac{g_{m1}}{\frac{g_{o1}}{\beta_1} + \frac{g_{o3}}{\beta_3}} \right]$$

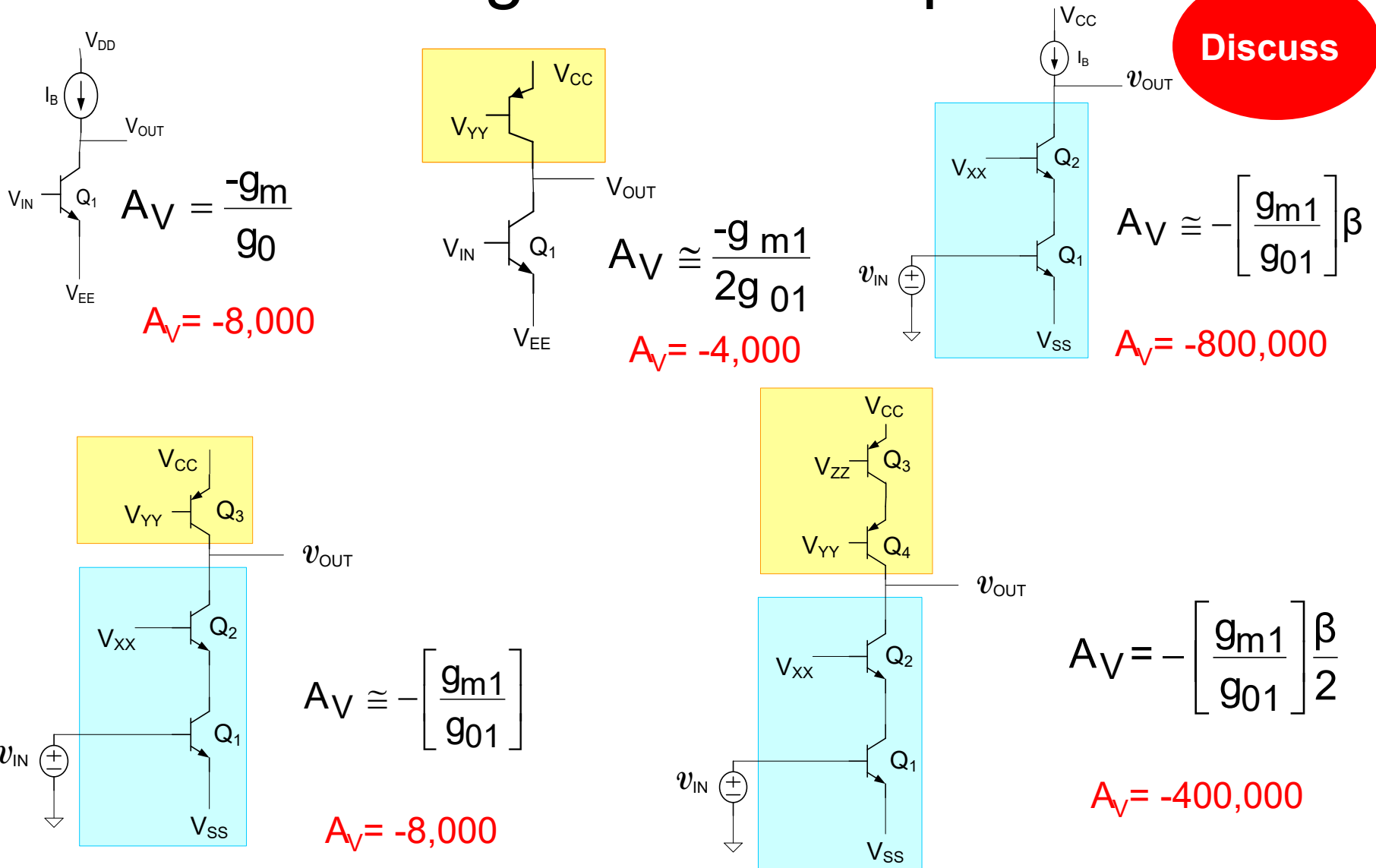
If $\beta_1 = \beta_3 = \beta$

$$A_V = - \left[\frac{g_{m1}}{g_{o1}} \right] \frac{\beta}{2}$$

$$A_V = - [8000] \frac{100}{2} \cong -400,000$$

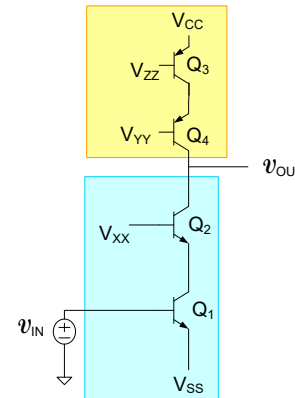
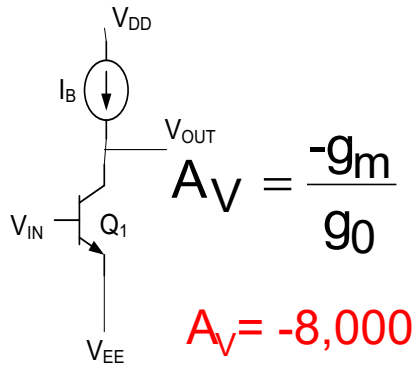
- This gain is very large and is a factor of 2 below that obtained with an ideal current source biasing
- Although the factor of 2 is not desired, the performance of this circuit is still very good
- This factor of 2 gain reduction is that same as was observed for the CE amplifier when a transistor-level current source was used
- Biasing voltages V_{ZZ} and V_{SS} are critical so seldom used single-ended but good biasing strategies exist for differential operation

Cascode Configuration Comparisons



Can we use more cascoding to further increase the gain?

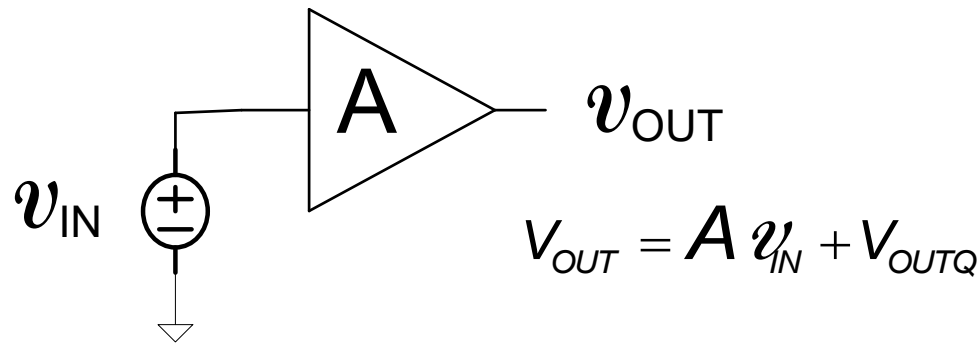
High Gain Amplifiers Seldom Used Open Loop



$$A_V = - \left[\frac{g_{m1}}{g_{01}} \right] \frac{\beta}{2}$$

$A_V = -400,000$

Discuss

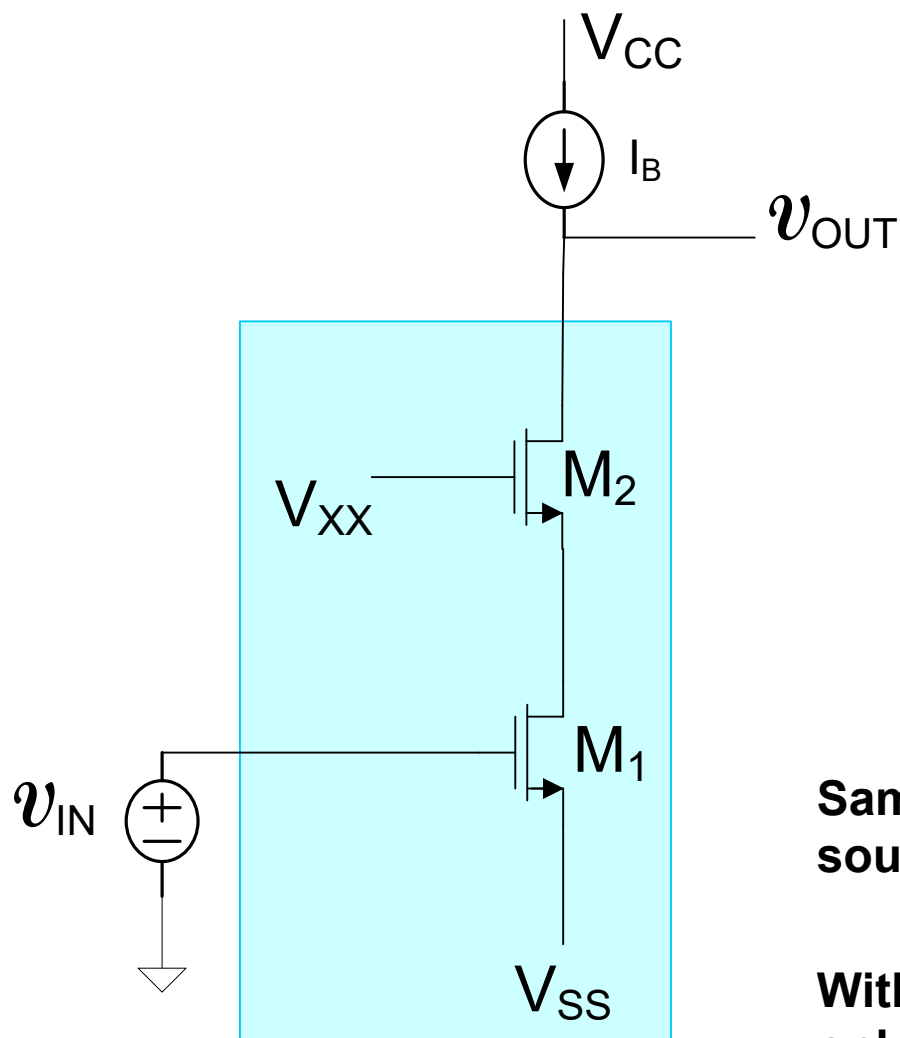


If $A_V = -400,000$ and V_{IN} increases by 1mV, what would happen at the output?

$|V_{OUT}|$ would increase by $400,000 \times 1\text{mV} = -400\text{V}$

The Cascode Amplifier (consider n-ch MOS version)

Discuss



$$A_{V_{CC}} \cong - \left[\frac{g_{m1} g_{m2}}{g_{o1} g_{o2}} \right]$$

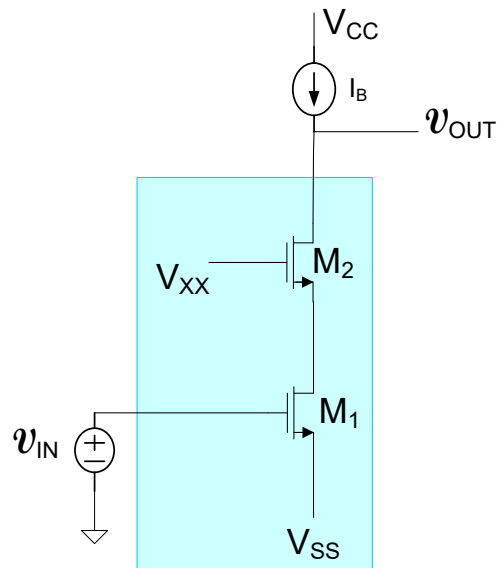
$$g_{oCC} \cong \left[\frac{g_{o1} g_{o2}}{g_{m2}} \right]$$

Same issues for biasing with current source as for BJT case

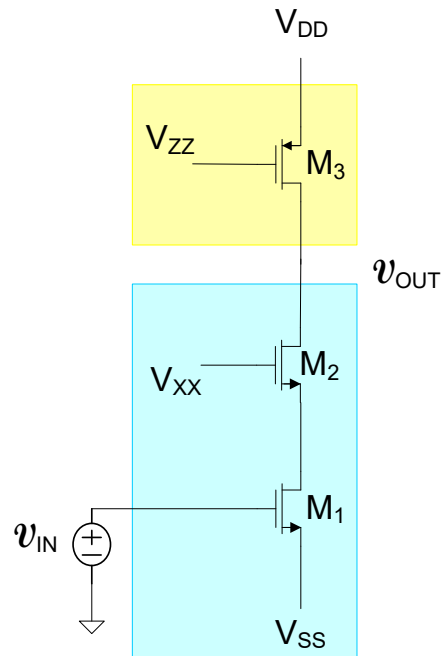
With cascode current source for I_B , gain only drops by a factor of 2 from value with ideal current source

The Cascode Amplifier (consider n-ch MOS version)

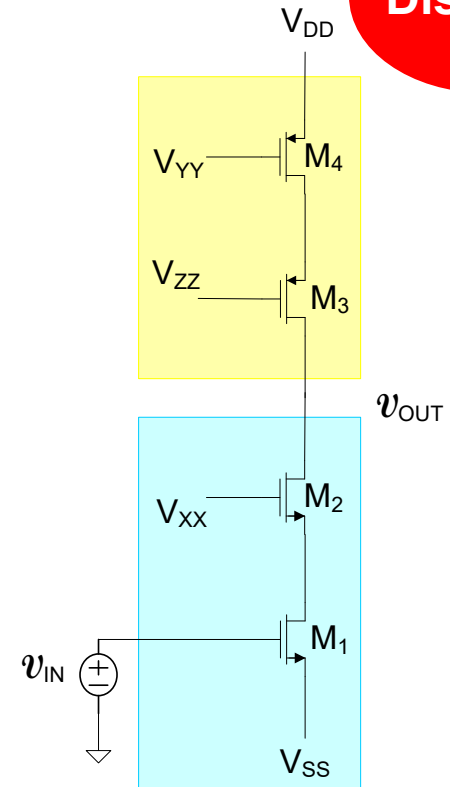
Discuss



$$A_{VCC} \cong - \left[\frac{g_{m1} g_{m2}}{g_{o1} g_{o2}} \right]$$



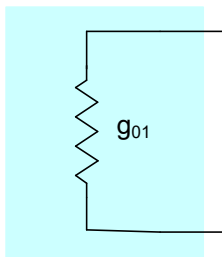
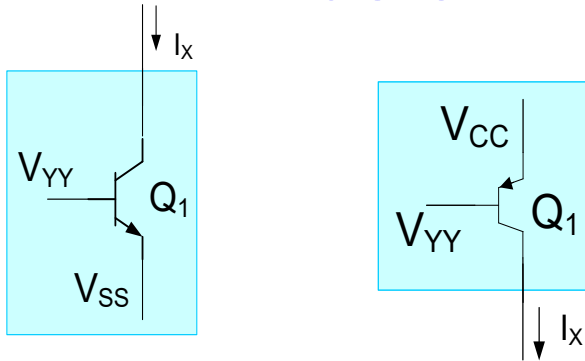
$$A_{VCC} \cong - \left[\frac{g_{m1}}{g_{o1}} \right]$$



$$A_{VCC} \cong - \frac{1}{2} \left[\frac{g_{m1} g_{m2}}{g_{o1} g_{o2}} \right]$$

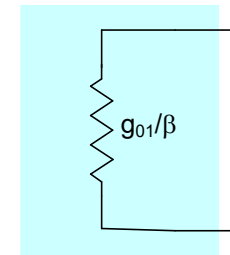
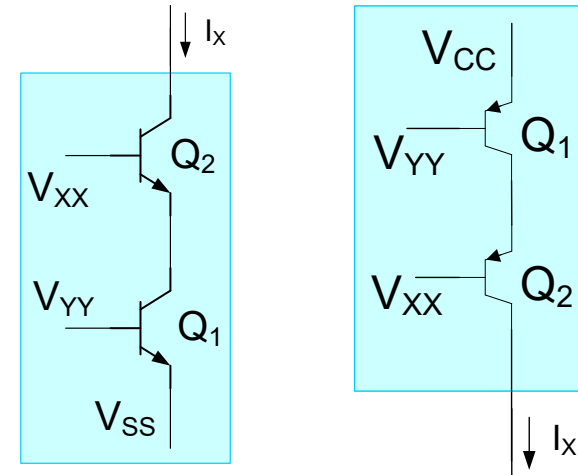
Current Source Summary (BJT)

Basic

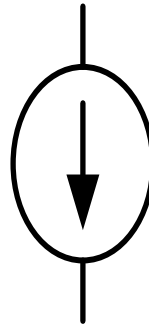


$$g_0 \cong g_{01}$$

Cascode

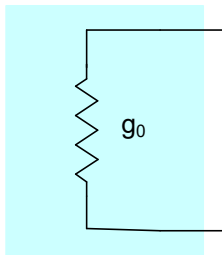
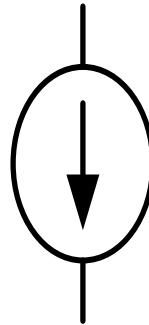
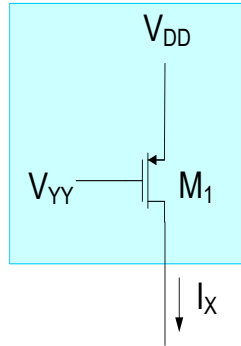
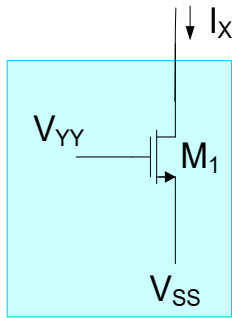


$$g_{0CC} \cong \frac{g_{01}}{\beta}$$



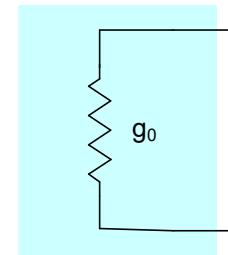
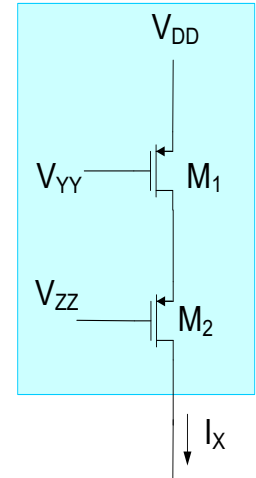
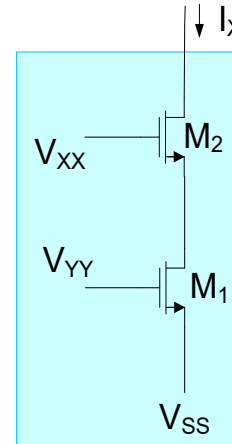
Current Source Summary (MOS)

Basic



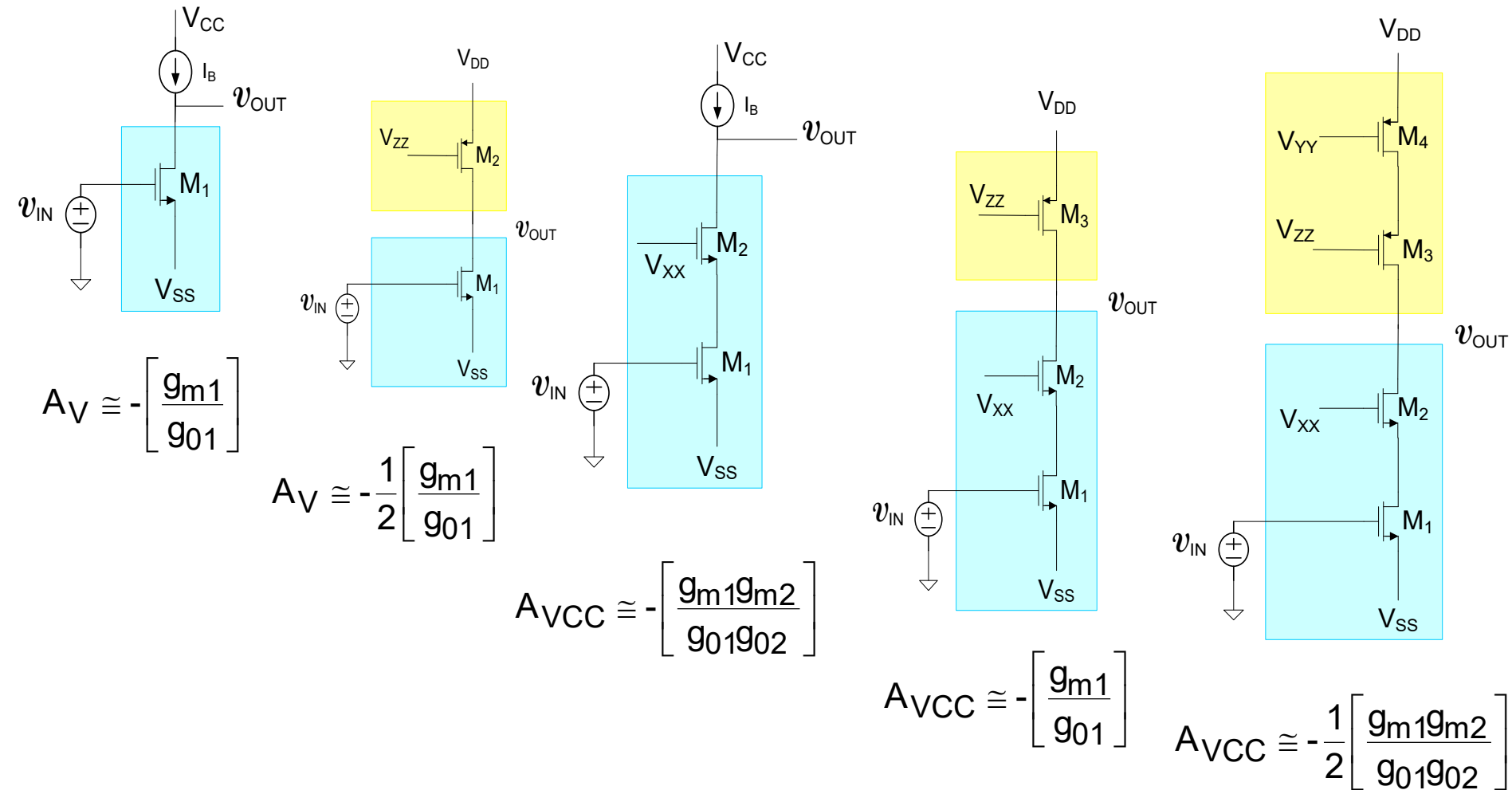
$$g_0 \cong g_{01}$$

Cascode

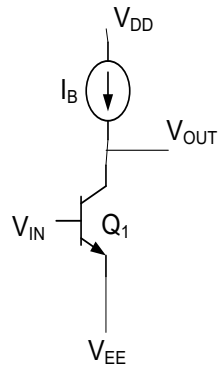


$$g_0 \cong g_{01} \frac{g_{02}}{g_{m2}}$$

High Gain Amplifier Comparisons (n-ch MOS)



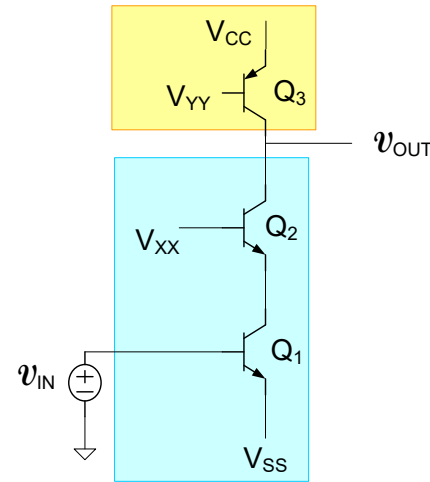
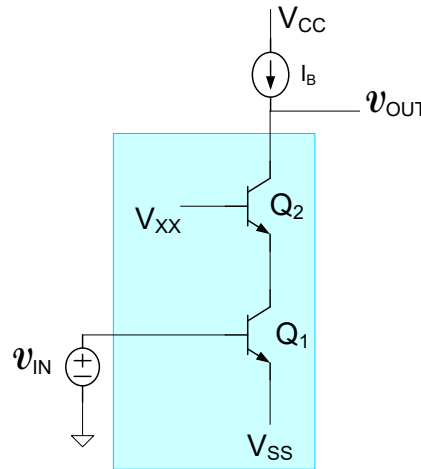
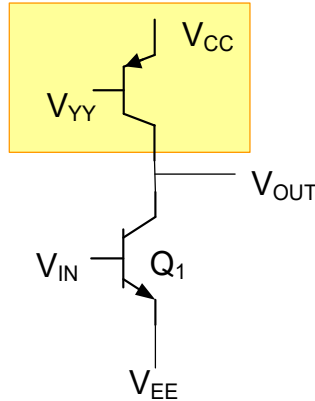
High Gain Amplifier Comparisons (BJT)



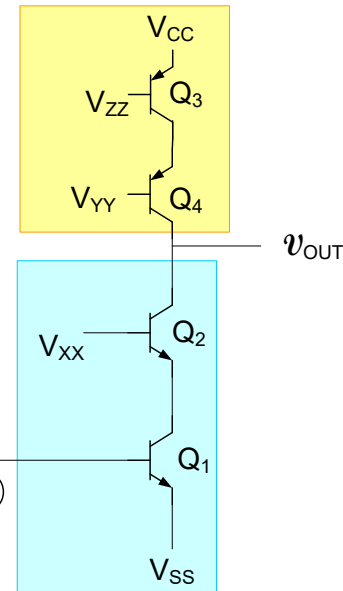
$$A_V = \frac{-g_m}{g_0}$$

$$A_V \cong -\frac{1}{2} \frac{g_{m1}}{g_{01}}$$

$$A_V \cong -\left[\frac{g_{m1}}{g_{01}} \right] \beta$$



$$A_V \cong -\left[\frac{g_{m1}}{g_{01}} \right]$$



$$A_V = -\left[\frac{g_{m1}}{g_{01}} \right] \frac{\beta}{2}$$

- Single-ended high-gain amplifiers inherently difficult to bias (because of the high gain)
- Biasing becomes practical when used in differential applications
- These structures are widely used but usually with differential inputs



Stay Safe and Stay Healthy !

End of Lecture 34